

Electronic and Transport Properties of Graphene

Tsuneya ANDO

1. Introduction

- Weyl's equation for neutrino
- Berry's phase and topological anomaly

2. Singular diamagnetic susceptibility

- Band-gap effect
- Spatially varying magnetic field

3. Transport properties graphene

- Singularities at Dirac point
- Long-range scatterers

4. Multi-layer graphene

- Bilayer graphene
- Hamiltonian decomposition

5. Future outlook

- Gauge fields
- Chiral edge states

6. Summary

Nara, Jun 4 (Tue) 2013



Collaborators

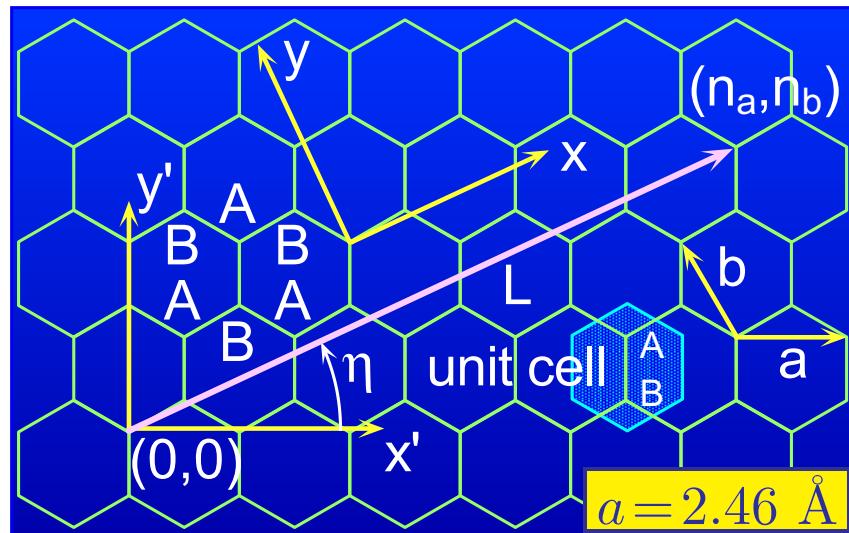
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 Masaki NORO (TITech)
 Mikito KOSHINO (Tohoku Univ)



16th International Workshop on Computational
 Electronics, Nara Prefectural New Public Hall
 Jun 4 (Tue) – 7 (Fri) 2013 [13:30–14:30 (50+10)]

Effective-Mass Description: Neutrino or Massless Dirac Electron

Graphene (Triangular antidot lattice)



Weyl's equation for neutrino (K)

$$\Leftrightarrow \gamma(\boldsymbol{\sigma} \cdot \hat{\mathbf{k}}) \mathbf{F}(\mathbf{r}) = \varepsilon \mathbf{F}(\mathbf{r})$$

$$\Leftrightarrow \gamma(\sigma_x \hat{k}_x + \sigma_y \hat{k}_y) \mathbf{F}(\mathbf{r}) = \varepsilon \mathbf{F}(\mathbf{r})$$

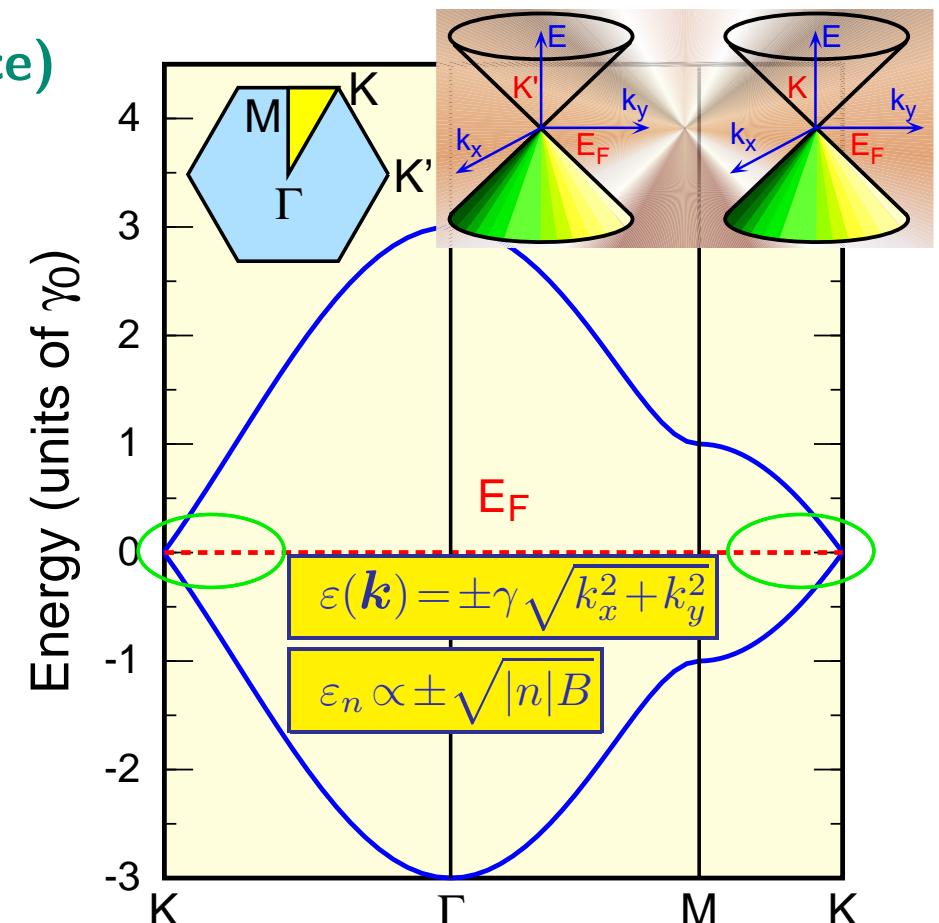
$$\begin{pmatrix} 0 & \gamma(\hat{k}_x - i\hat{k}_y) \\ \gamma(\hat{k}_x + i\hat{k}_y) & 0 \end{pmatrix} \begin{pmatrix} F^A(\mathbf{r}) \\ F^B(\mathbf{r}) \end{pmatrix} = \varepsilon \begin{pmatrix} F^A(\mathbf{r}) \\ F^B(\mathbf{r}) \end{pmatrix}$$

Massless (Dirac) $v_F \sim c/300$ ($\gamma_0 \sim 3$ eV)

Constant velocity (~light, cannot stop)

Topological anomaly

$\gamma = \sqrt{3}\gamma_0 a/2$ (γ_0 : Hopping integral) [Page 2]



Wave Vector

$$\hat{\mathbf{k}} = -i\vec{\nabla}$$

Velocity: $v_F = \gamma/\hbar$

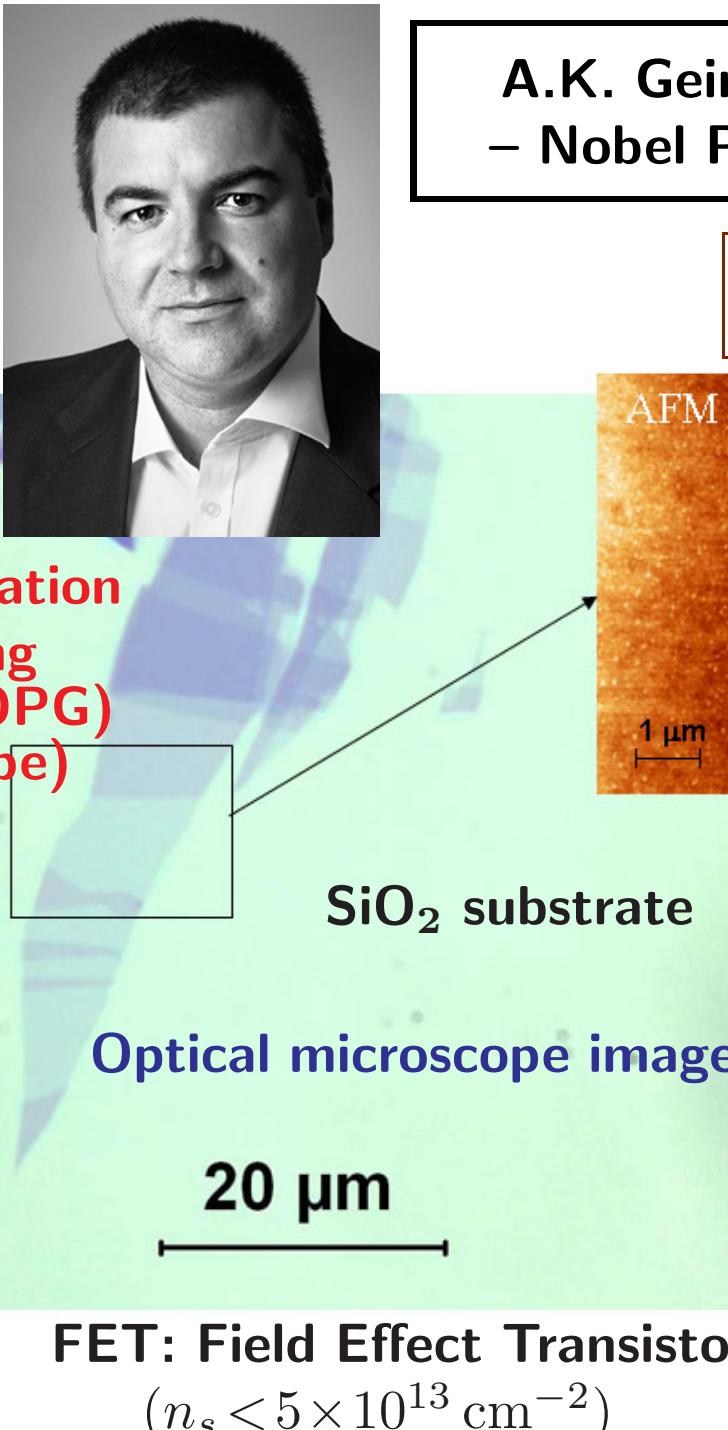
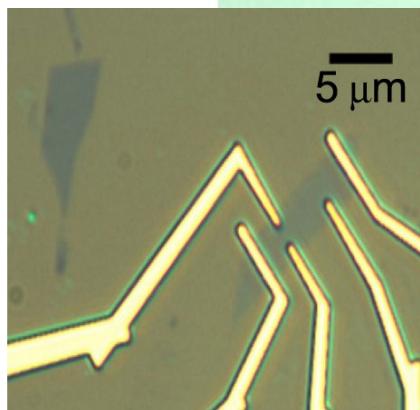
K' : $\sigma \rightarrow \sigma^*$

A.K. Geim & K.S. Novoselov
– Nobel Prize Physics 2010 –

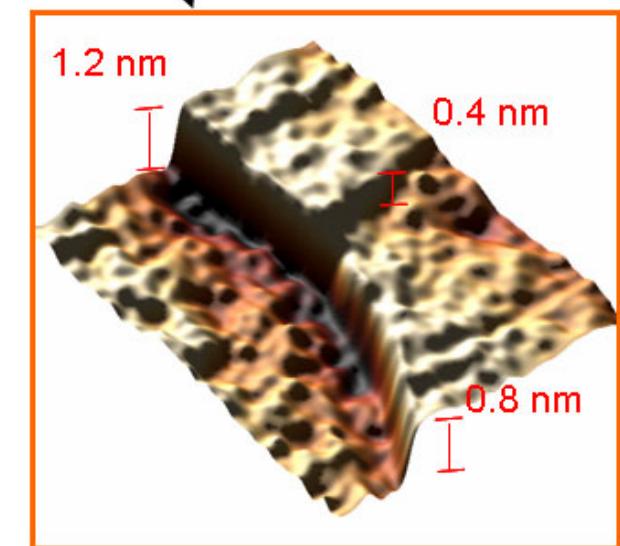
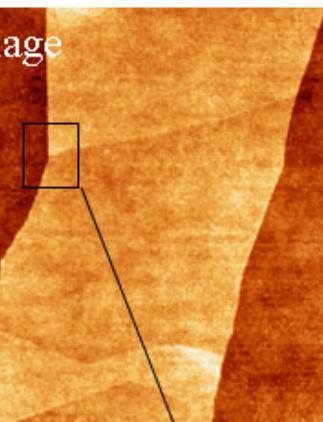
*K.S. Novoselov et al.,
Science 306, 666 (2004)*



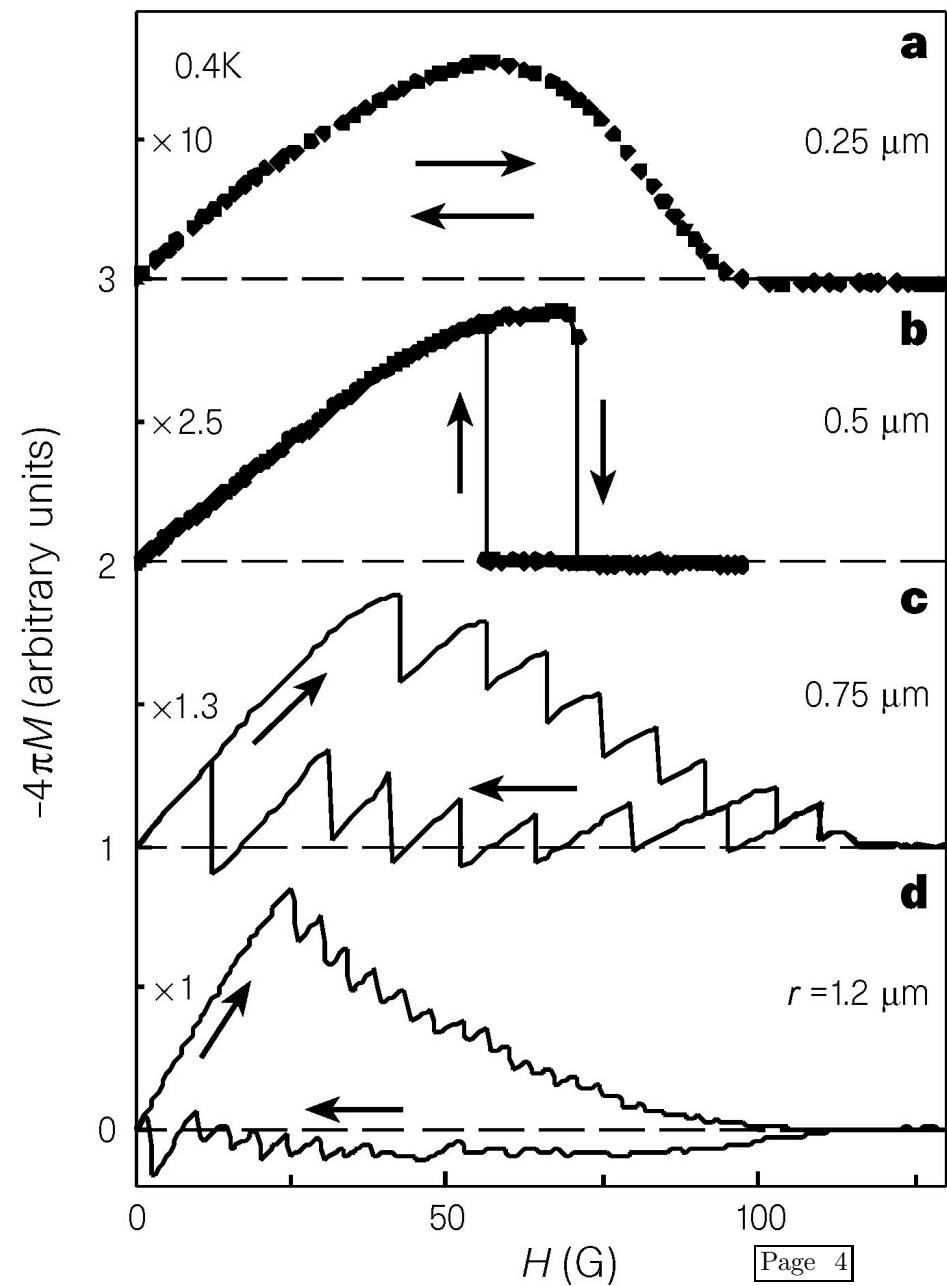
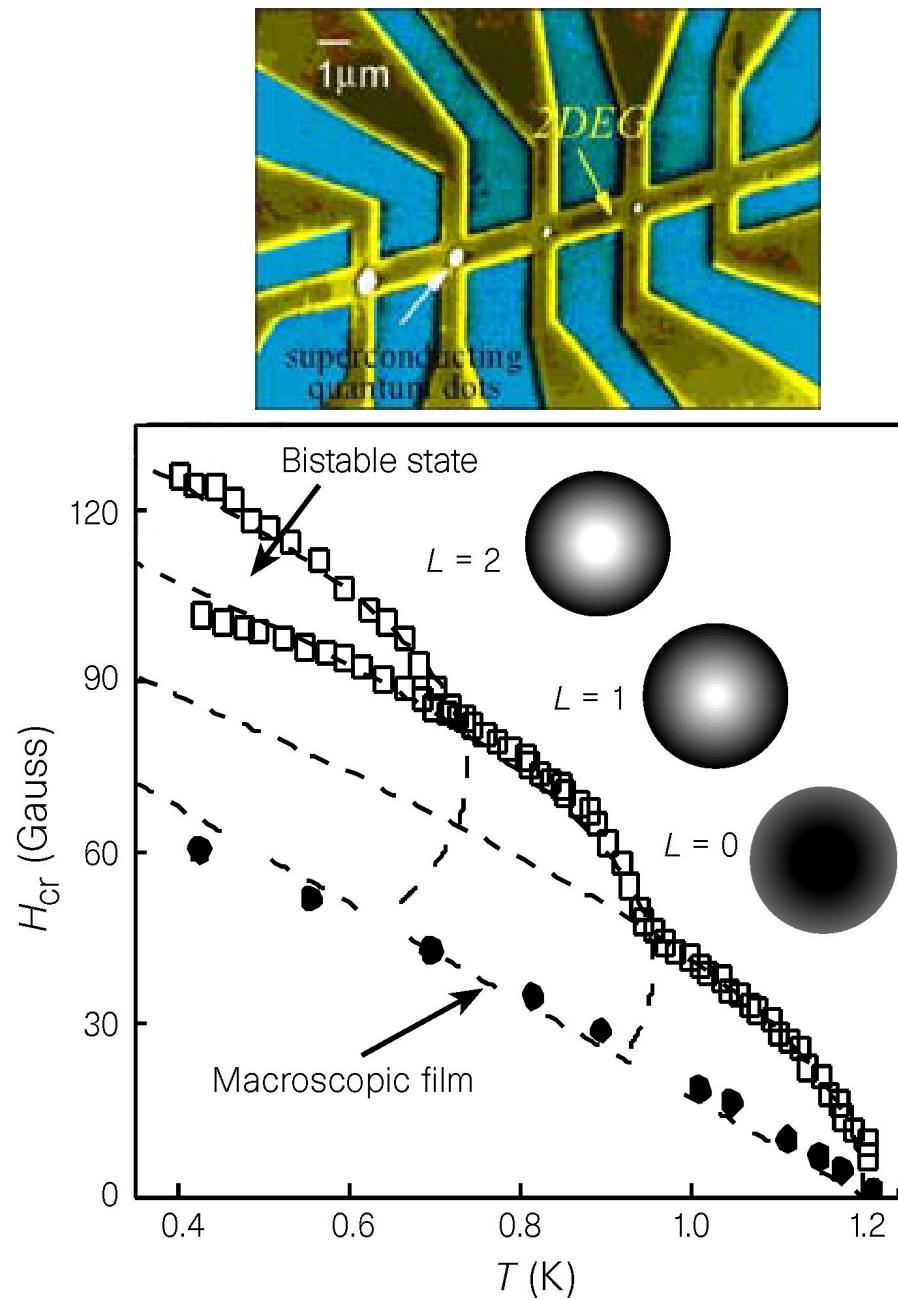
Mechanical exfoliation
(Repeated peeling
of graphite (HOPG)
using scotch tape)



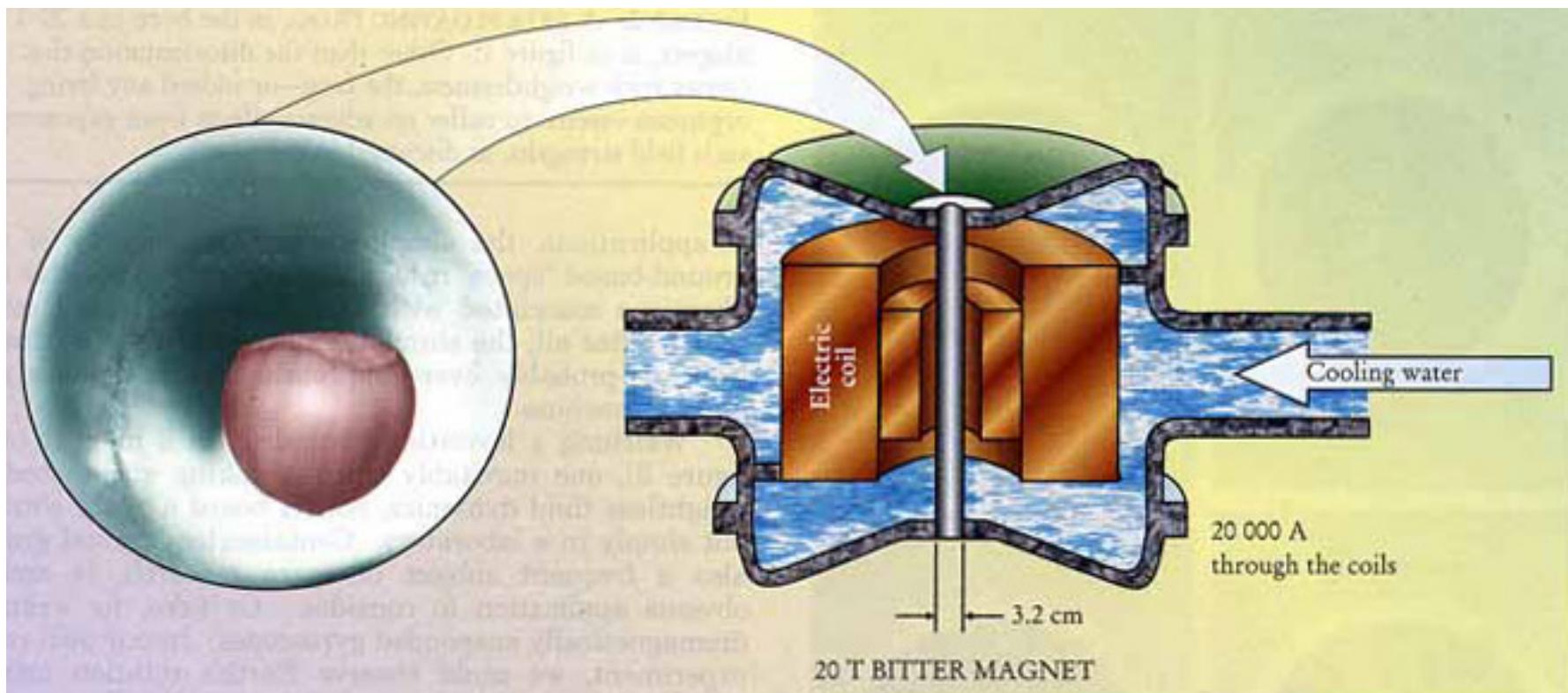
FET: Field Effect Transistor
($n_s < 5 \times 10^{13} \text{ cm}^{-2}$)



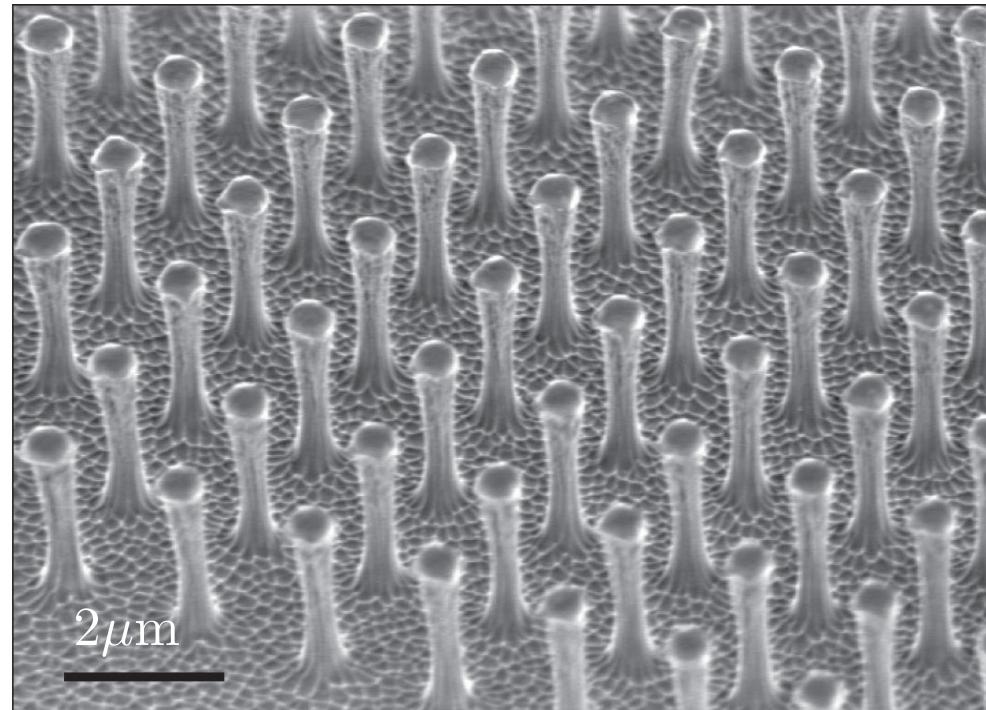
'Phase Transitions' in Small Superconductors (Nijmegen, ~1997)



Magnetic Levitation (Nijmegen, ~1998)



Gecko Tape (Manchester, ~2003)



Gecko (やもり)

Topological Anomaly and Berry's Phase

Weyl's equation : Neutrino \Leftrightarrow Helicity ($\sigma \leftrightarrow k$)

$$R(\theta) = \begin{pmatrix} e^{-i\theta/2} & 0 \\ 0 & e^{i\theta/2} \end{pmatrix}$$

$$\gamma(\boldsymbol{\sigma} \cdot \hat{\mathbf{k}}) F_{s\mathbf{k}}(\mathbf{r}) = \varepsilon_s(\mathbf{k}) F_{s\mathbf{k}}(\mathbf{r}) \quad F_{s\mathbf{k}}(\mathbf{r}) = \frac{e^{i\varphi_{\mathbf{k}}}}{\sqrt{2L^2}} \exp(i\mathbf{k} \cdot \mathbf{r}) R^{-1}[\theta(s\mathbf{k})] |s\rangle$$

$$R(\theta \pm 2\pi) = -R(\theta) \quad R(-\pi) = -R(+\pi)$$

$$\varepsilon_s(\mathbf{k}) = s\gamma|\mathbf{k}| \quad s = \pm 1$$

$$\psi(T) = e^{-i\zeta} \psi(0)$$

Pseudo spin \Rightarrow Berry's phase

$$\zeta = -i \int_0^T dt \left\langle s\mathbf{k}(t) \left| \frac{d}{dt} \right| s\mathbf{k}(t) \right\rangle = -\pi \quad \frac{1}{\sqrt{2}} \begin{pmatrix} s \\ e^{i\theta} \end{pmatrix}$$

Landau levels at $\varepsilon=0$ [J.W. McClure, PR 104, 666 (1956)]

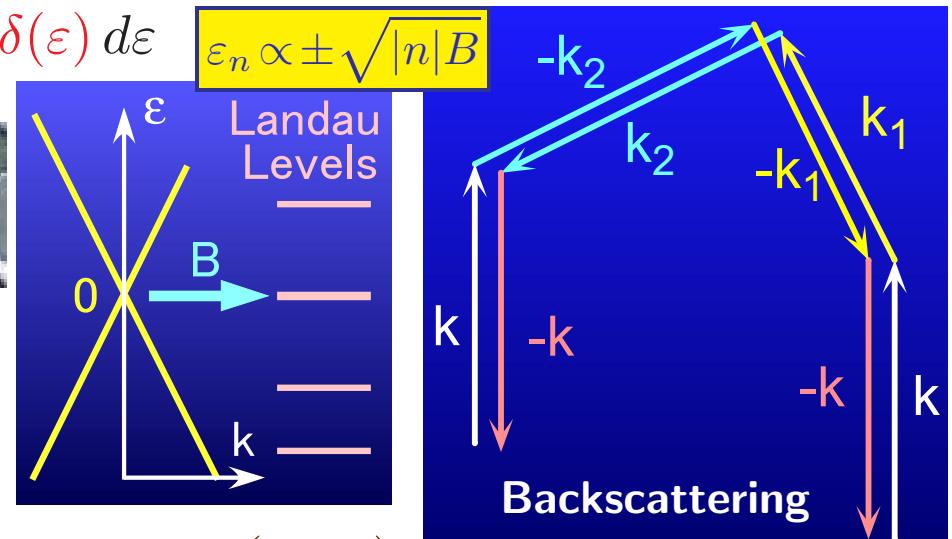
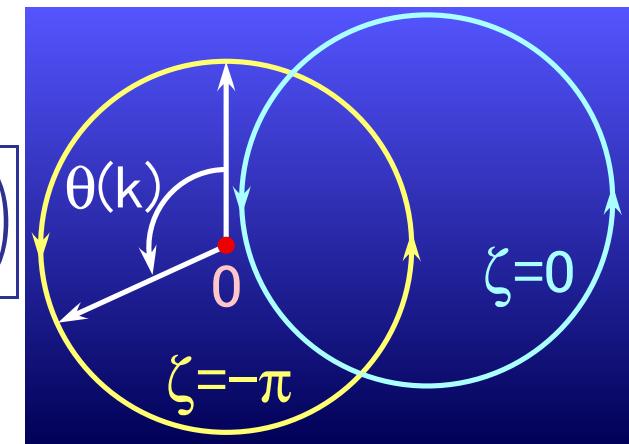
$$\chi = -\frac{g_v g_s \gamma^2}{6\pi} \left(\frac{e}{c\hbar} \right)^2 \int \left(-\frac{\partial f(\varepsilon)}{\partial \varepsilon} \right) \delta(\varepsilon) d\varepsilon \quad \varepsilon_n \propto \pm \sqrt{|n|B}$$



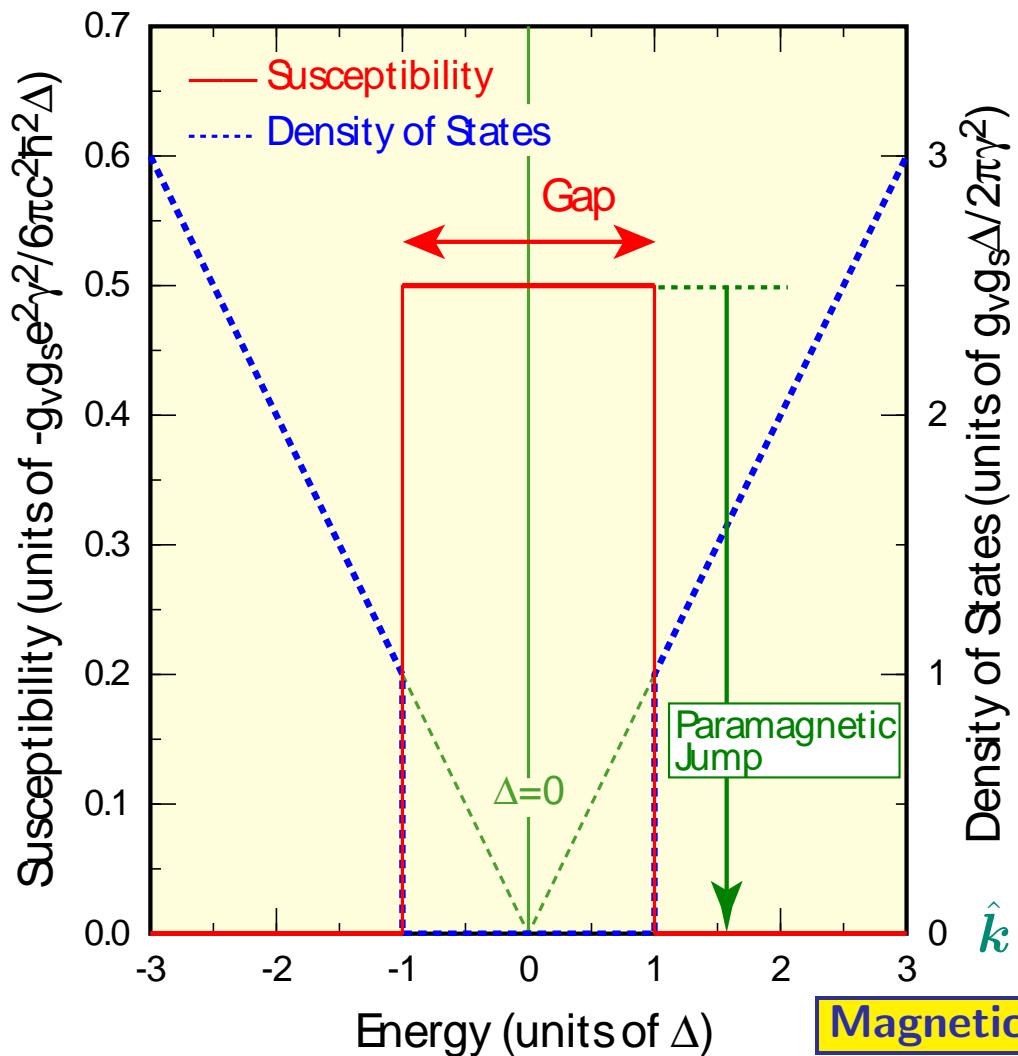
Absence of backscattering

Metallic CN with scatterers
 \Rightarrow **Perfect conductor**

T. Ando & T. Nakanishi, JPSJ 67, 1704 (1998)

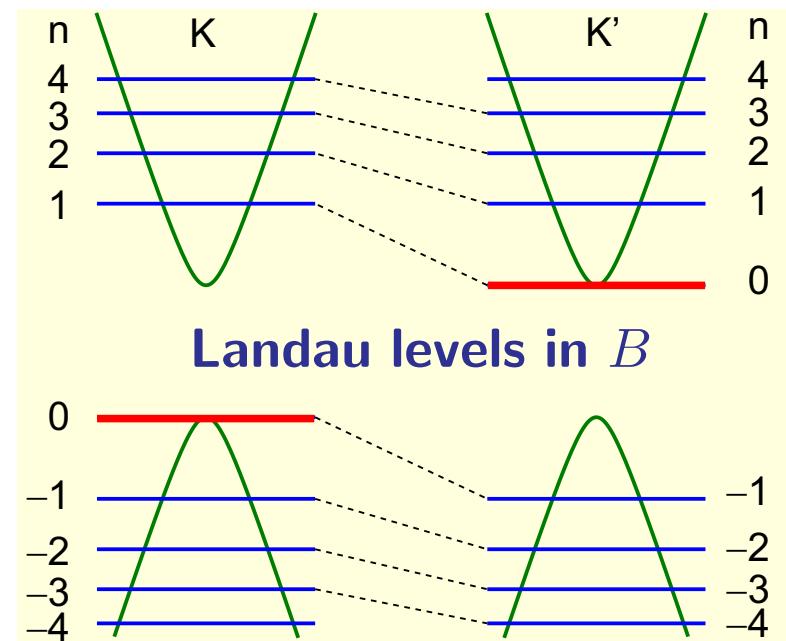


Band-Gap Effect [M. Koshino & T. Ando, PRB 81, 195431 (2010)]



Graphene with a gap

$$\begin{pmatrix} \Delta & \gamma \hat{k}_- \\ \gamma \hat{k}_+ & -\Delta \end{pmatrix} \Rightarrow \chi(\varepsilon) = -\frac{g_v g_s e^2 \gamma^2}{6\pi c^2 \gamma^2} \frac{\theta(\Delta - |\varepsilon|)}{2\Delta} \xrightarrow{\delta(\varepsilon)}$$



Hamiltonian at band edge

$$\mathcal{H} = \frac{\hbar^2 \hat{k}^2}{2m^*} \pm \frac{e\hbar}{2m^* c} B \quad m^* = \frac{\hbar^2 \Delta}{\gamma^2}$$

$$\chi_P(\varepsilon) = + \left(\frac{e\hbar}{2m^* c} \right)^2 D(\varepsilon)$$

$$\chi_L(\varepsilon) = - \frac{1}{3} \left(\frac{e\hbar}{2m^* c} \right)^2 D(\varepsilon)$$

$$D(\varepsilon) = \frac{g_s g_v m^*}{2\pi \hbar^2}$$

Diamagnetic Susceptibility of Spatially Varying Field

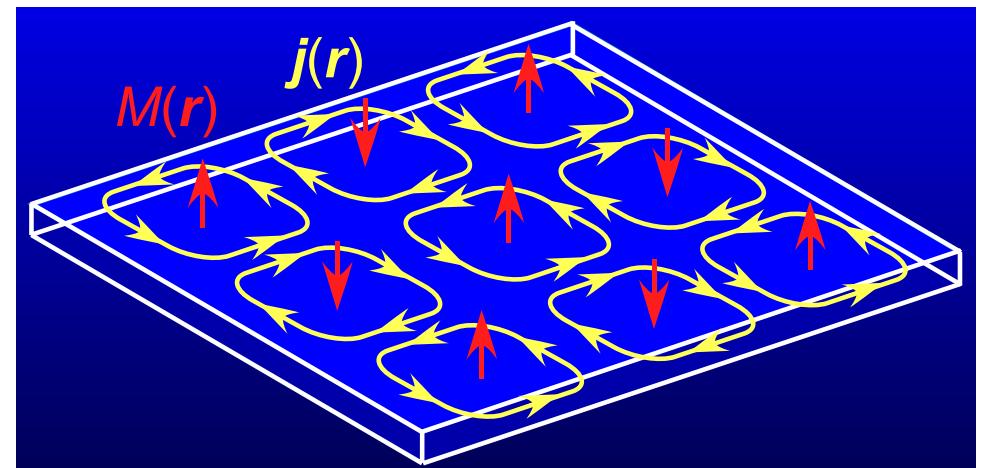
Induced current $\hat{K}(\mathbf{r}) = (K_{\mu\nu}(\mathbf{r}))$

$$\mathbf{j}(\mathbf{r}) = \int \hat{K}(\mathbf{r} - \mathbf{r}') \mathbf{A}(\mathbf{r}') d\mathbf{r}' \\ \Leftrightarrow \mathbf{j}(\mathbf{q}) = \hat{K}(\mathbf{q}) \mathbf{A}(\mathbf{q})$$

Gauge invariance

Current conservation

$$K_{\mu\nu}(\mathbf{q}) = \textcolor{red}{K}(\mathbf{q}) \left[\delta_{\mu\nu} - \frac{q_\mu q_\nu}{q^2} \right]$$



Magnetic moment: $M(\mathbf{r}) \Leftrightarrow \mathbf{j}(\mathbf{r}) = c(\nabla \times \hat{z})M(\mathbf{r}) \quad H(\mathbf{r}) = \nabla \times \mathbf{A}(\mathbf{r})$

Diamagnetic susceptibility: $\chi(\mathbf{q}) = \frac{1}{cq^2} \textcolor{red}{K}(\mathbf{q}) \Leftrightarrow M(\mathbf{q}) = \chi(\mathbf{q})H(\mathbf{q})$

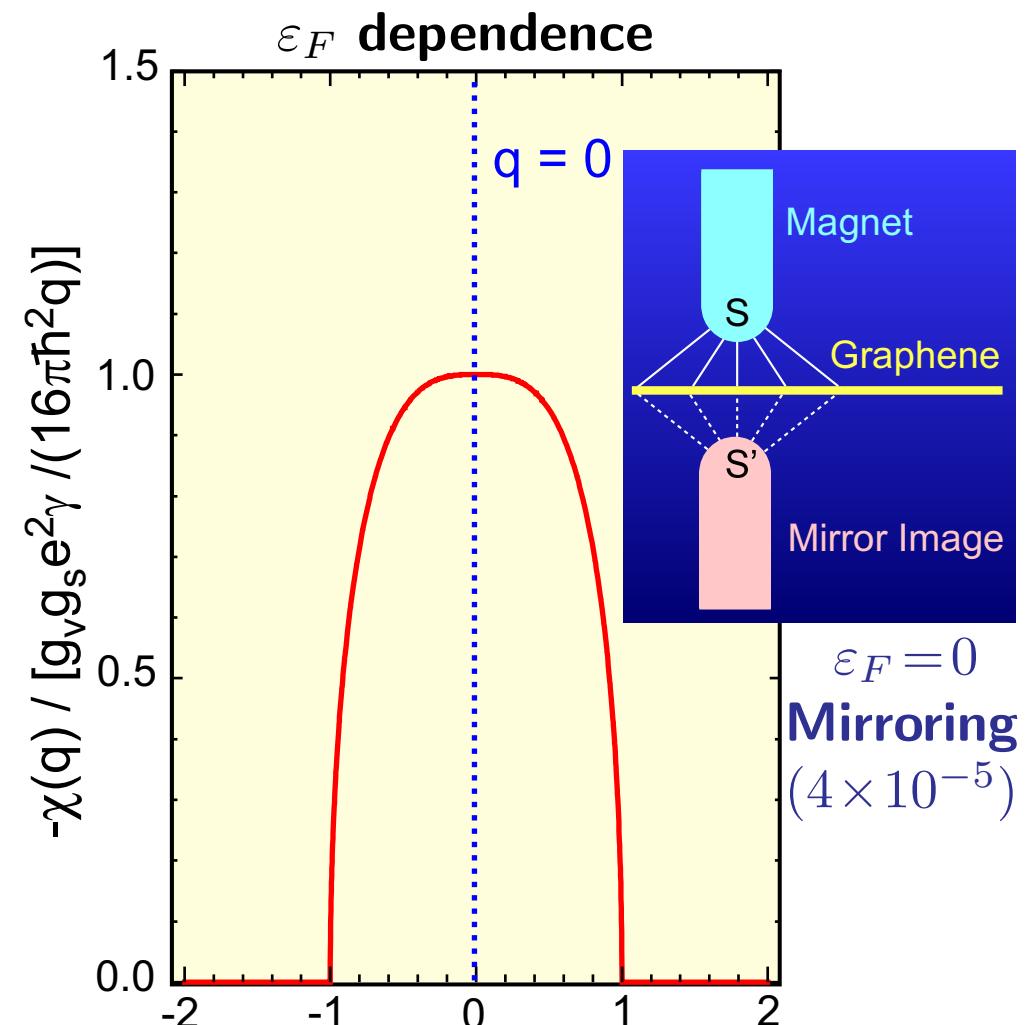
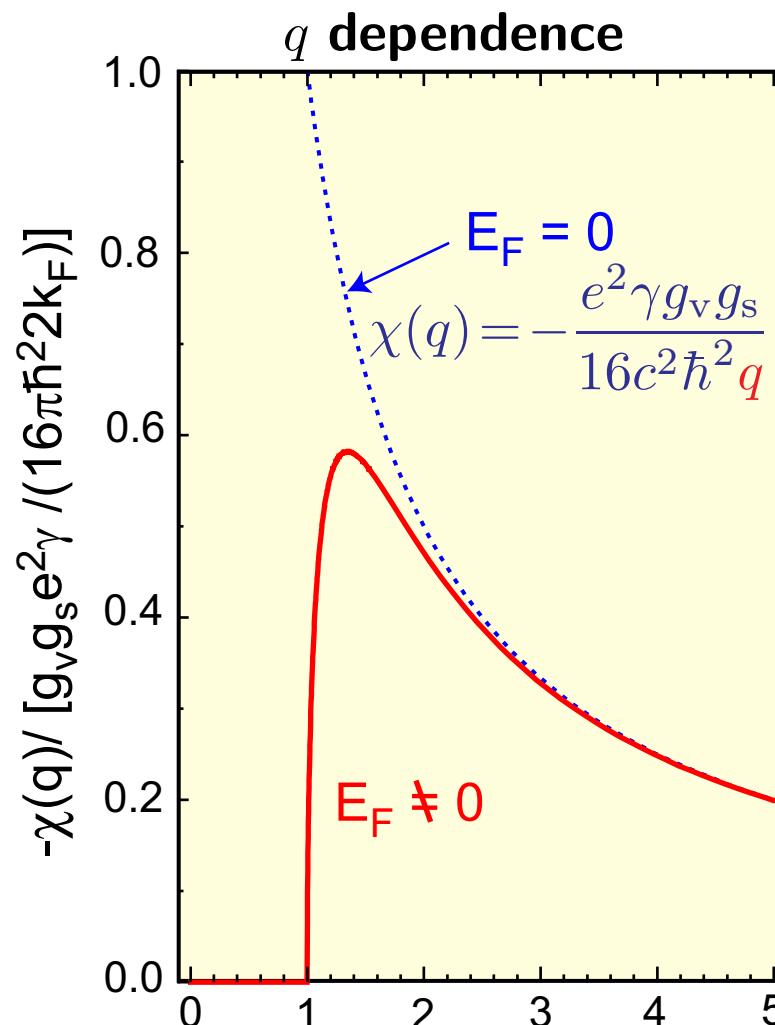
$$\chi(q) = -\frac{e^2 \gamma g_v g_s}{16c^2 \hbar^2} \frac{1}{q} \theta(q - 2k_F) \left[1 + \frac{2}{\pi} \frac{2k_F}{q} \sqrt{1 - \left(\frac{2k_F}{q} \right)^2} - \frac{2}{\pi} \sin^{-1} \left(\frac{2k_F}{q} \right) \right]$$

$$\Rightarrow \chi(q) = \begin{cases} 0 & (q < 2k_F) \\ \sim q^{-1} & (q > 2k_F) \end{cases} \quad \int_{-\infty}^{\infty} \chi(q; \varepsilon_F) d\varepsilon_F = -\frac{g_v g_s \gamma^2}{6\pi} \left(\frac{e}{c\hbar} \right)^2$$

$$\textbf{2DEG: } \chi(q) = -\frac{e^2 g_v g_s}{24\pi m^* c^2} \left(1 - \left[1 - \left(\frac{2k_F}{q} \right)^2 \right]^{3/2} \theta(q - 2k_F) \right)$$

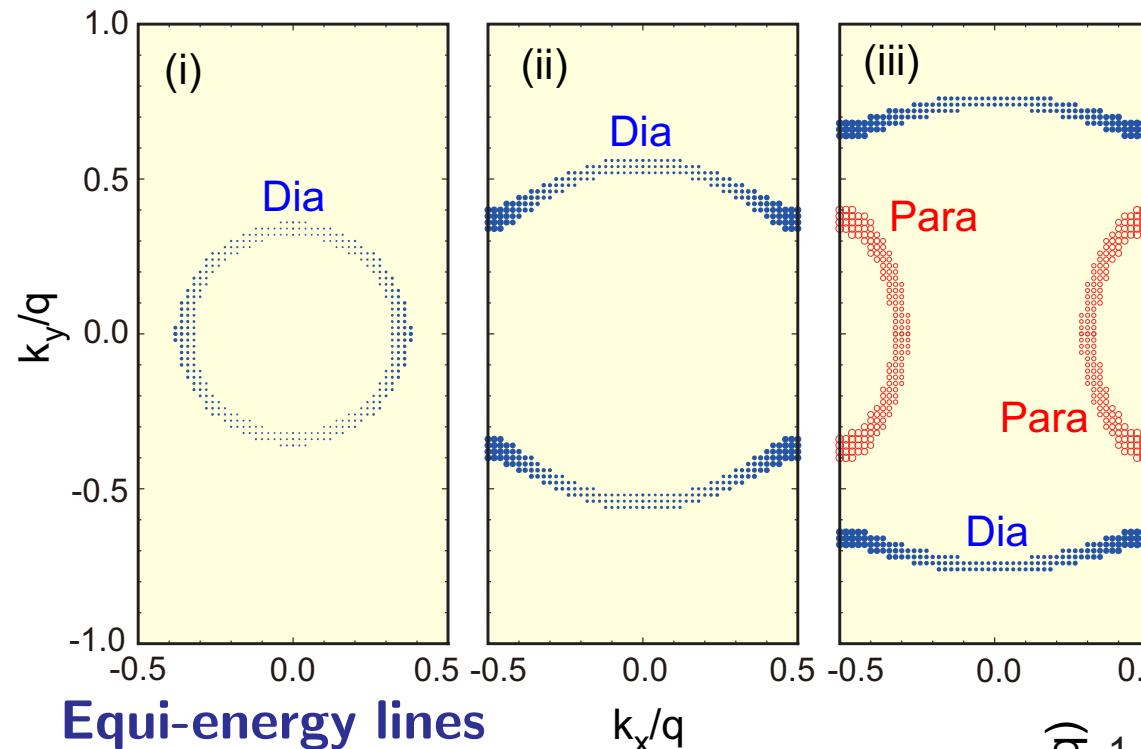
Diamagnetic Susceptibility $\chi(q)$ of Spatially Varying Field

M. Koshino, Y. Arimura, and T. Ando, PRL 102, 177203 (2009)



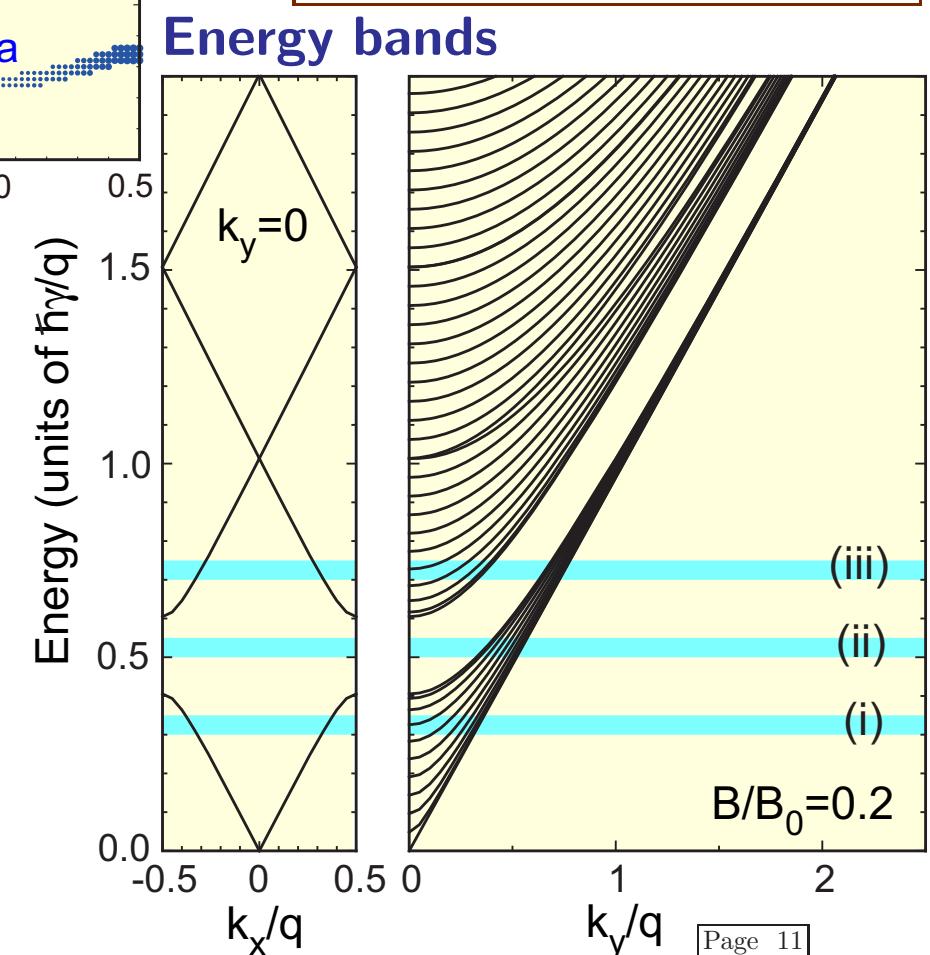
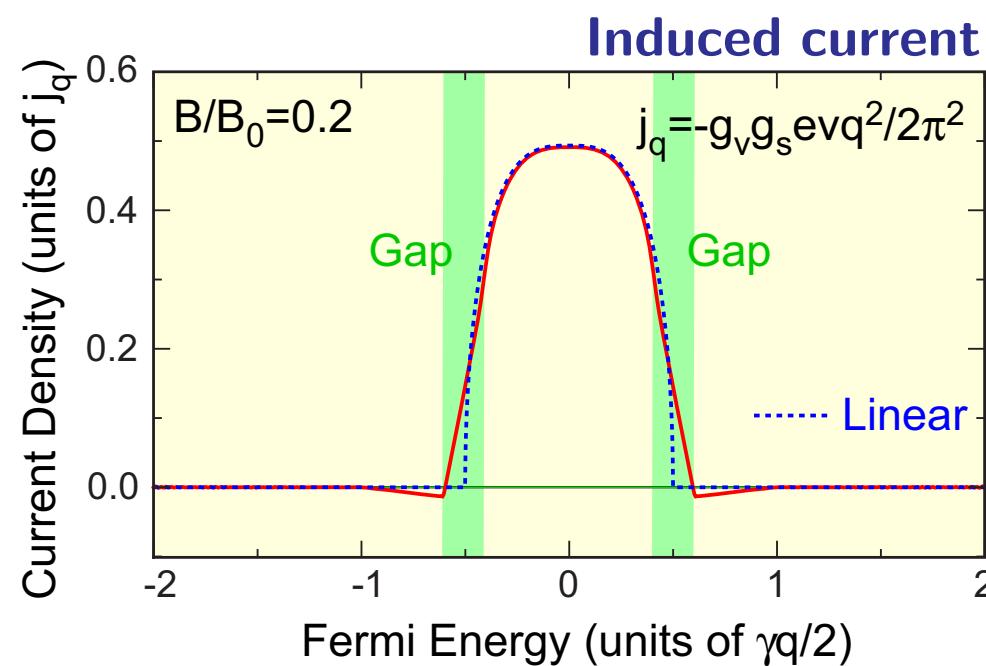
No response to
slowly-varying field $q/(2k_F)$

Uniform limit: $\lim_{q \rightarrow 0} \chi(q) = -\frac{g_v g_s \gamma^2}{6\pi} \left(\frac{e}{c\hbar}\right)^2 \delta(\varepsilon_F)$



Magnetic Superlattice
M. Koshino & T. Ando,
Solid State Commun.
151, 1054 (2011)

cf. C.H. Park et al., *PRL*
101, 126804 (2008), ...



Zero-Mode Anomaly in Conductivity

Density of states: $D(\varepsilon) = \frac{|\varepsilon|}{2\pi\gamma^2} \Rightarrow$ **Zero-gap semiconductor**

Boltzmann conductivity

$$\sigma(\varepsilon_F) = g_s g_v e^2 D^* D(\varepsilon_F) = \frac{g_s g_v}{4} \frac{e^2}{\pi^2 \hbar} \frac{1}{W}$$

Einstein relation

$$D^* = v_F^2 \tau = \frac{\gamma^2}{\hbar^2} \tau \quad W = \frac{n_i u^2}{4\pi\gamma^2} \ll 1$$

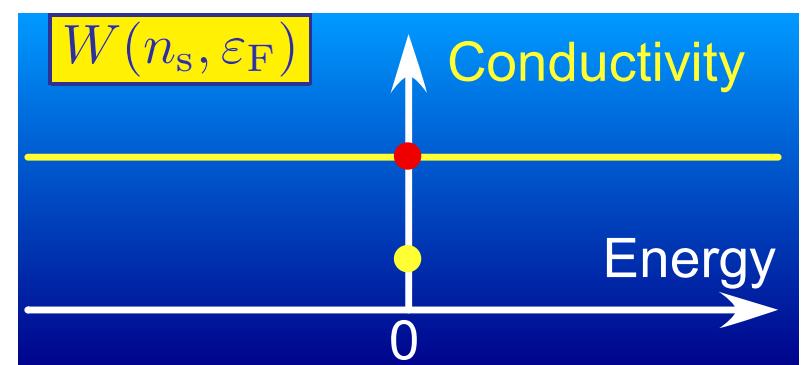
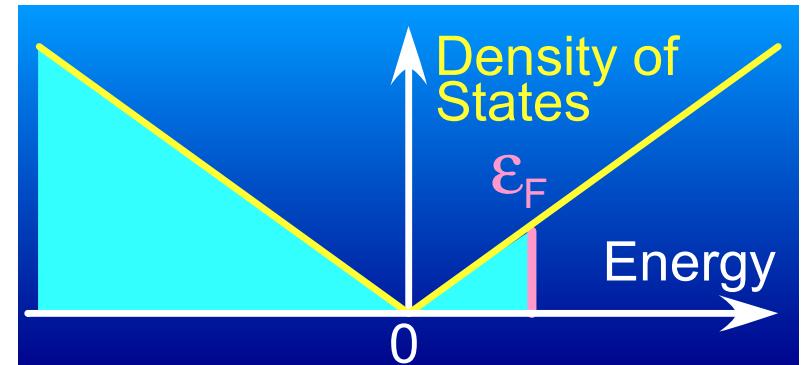
$$\frac{1}{\tau} = \frac{2\pi}{\hbar} n_i u^2 D(\varepsilon_F) \propto 2\pi W |\varepsilon_F| / \hbar$$

$$\tau \propto D(\varepsilon_F)^{-1} \quad \begin{matrix} u & \text{Impurity strength} \\ n_i & \text{Impurity density} \end{matrix}$$

\Rightarrow **Metal!**

Short-range ($k_F d \ll 1$)

$\Rightarrow \sigma(0)$ for $D(0)=0$ ($\Rightarrow 2e^2/\pi^2 \hbar$)



Singularity at the Dirac point ($\varepsilon_F=0$) \Leftrightarrow Fermi energy scaling

$$\sigma_{xx}(B) = \sigma_{xx} \left(\frac{\hbar\omega_B}{\varepsilon_F} \right) \quad \boxed{\hbar\omega_B \propto \sqrt{B}}$$

$$\sigma_{xy}(B) = \sigma_{xy} \left(\frac{\hbar\omega_B}{\varepsilon_F} \right)$$

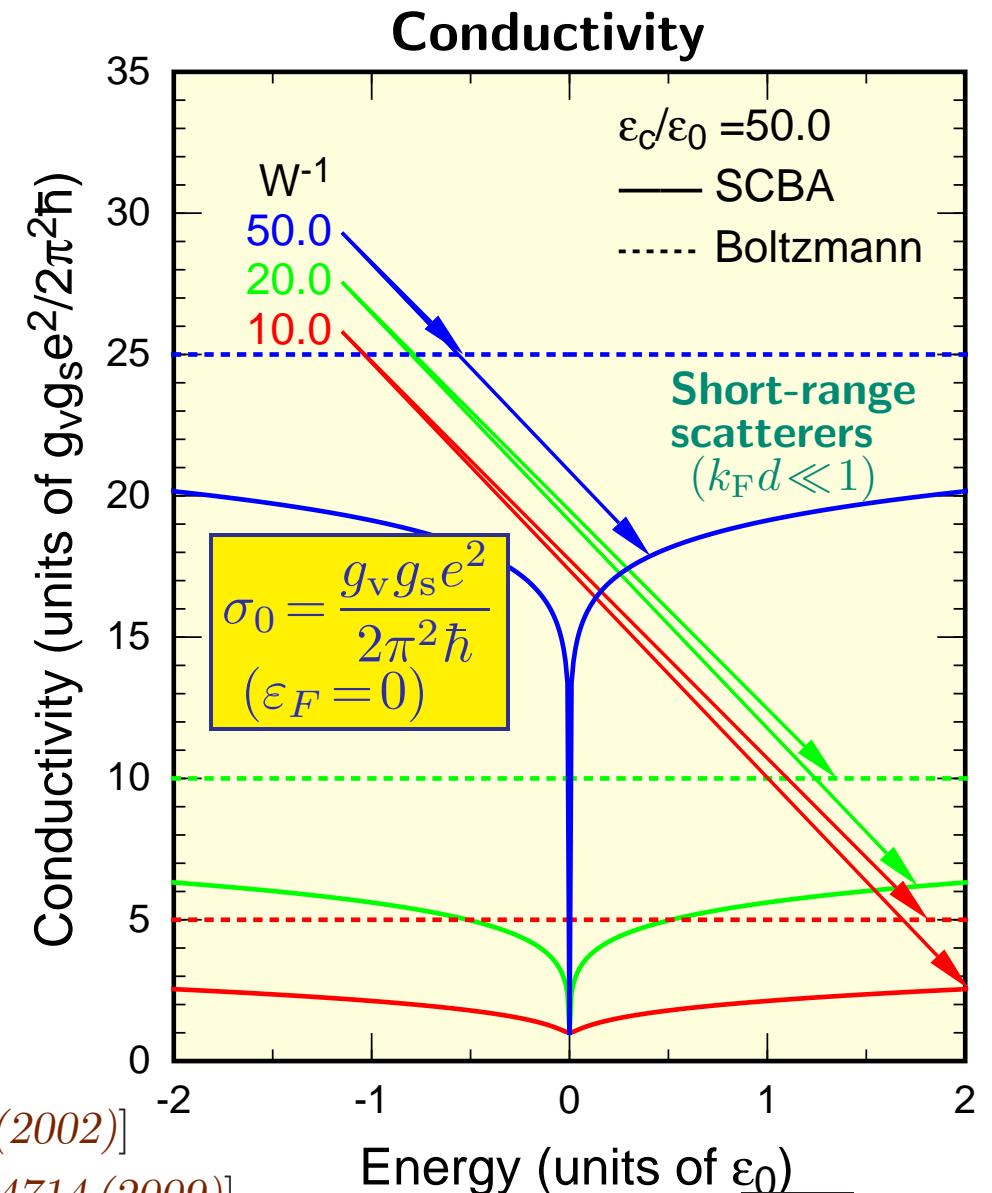
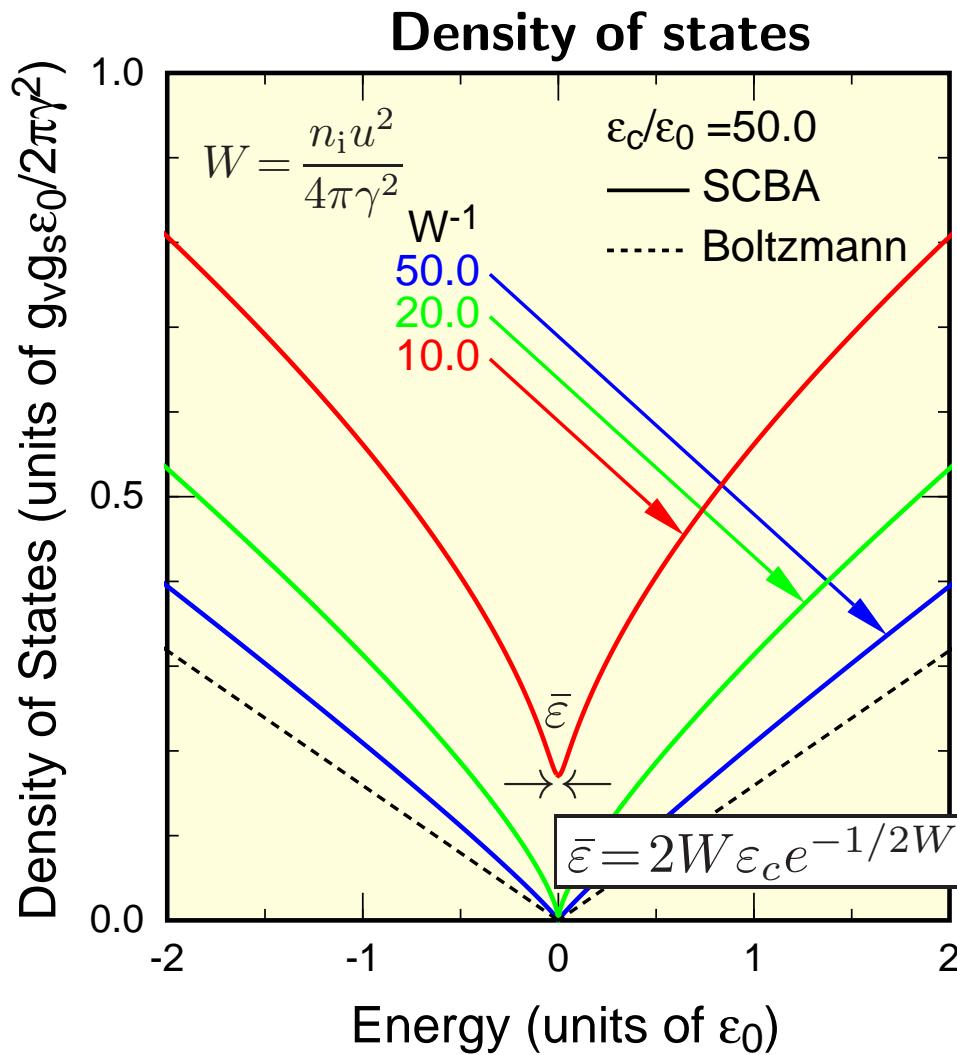
Magnetoconductivity

$$\sigma(\omega) = \sigma \left(\frac{\hbar\omega}{\varepsilon_F} \right) = \begin{cases} \frac{g_s g_v}{4} \frac{e^2}{2\pi^2 \hbar W} & (\omega=0) \\ \frac{g_v g_s}{4} \frac{e^2}{4\hbar} & (\hbar\omega/\varepsilon_F \gg 1) \end{cases}$$

Dynamical conductivity

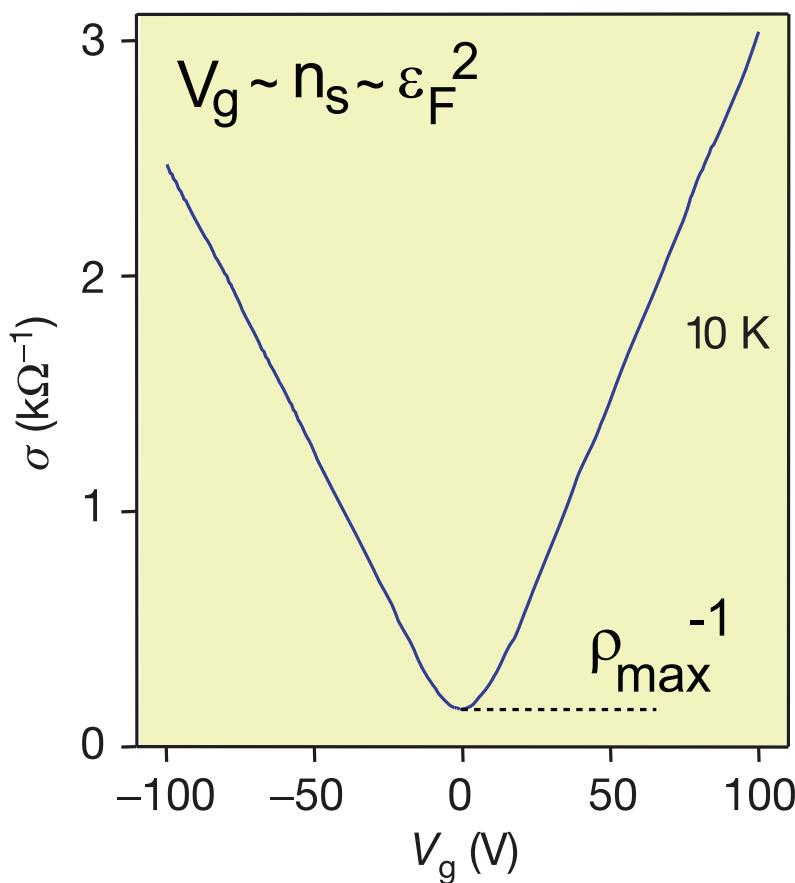
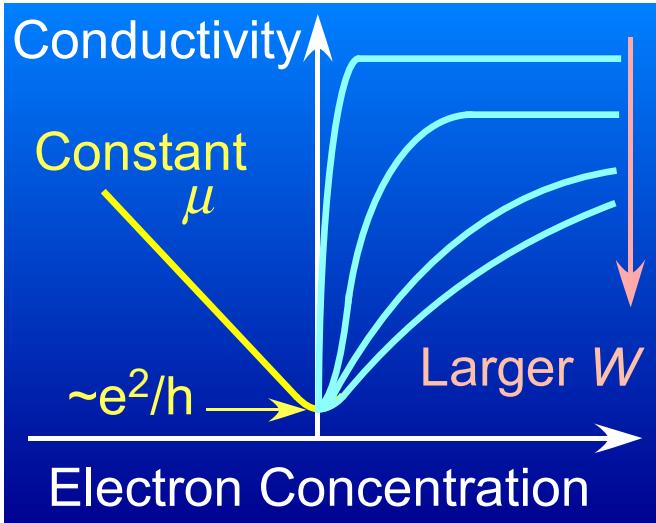
Self-Consistent Born Approximation

[N.H. Shon and T. Ando, *J. Phys. Soc. Jpn.* 67, 2421 (1998)]



QHE [Y. Zheng & T. Ando, *PRB* 65, 245420 (2002)]

Hall effect [T. Fukuzawa et al., *JPSJ* 78, 094714 (2009)]



Conductivity vs Carrier Concentration

K.S. Novoselov et al., *Nature* 438, 197 (2005)

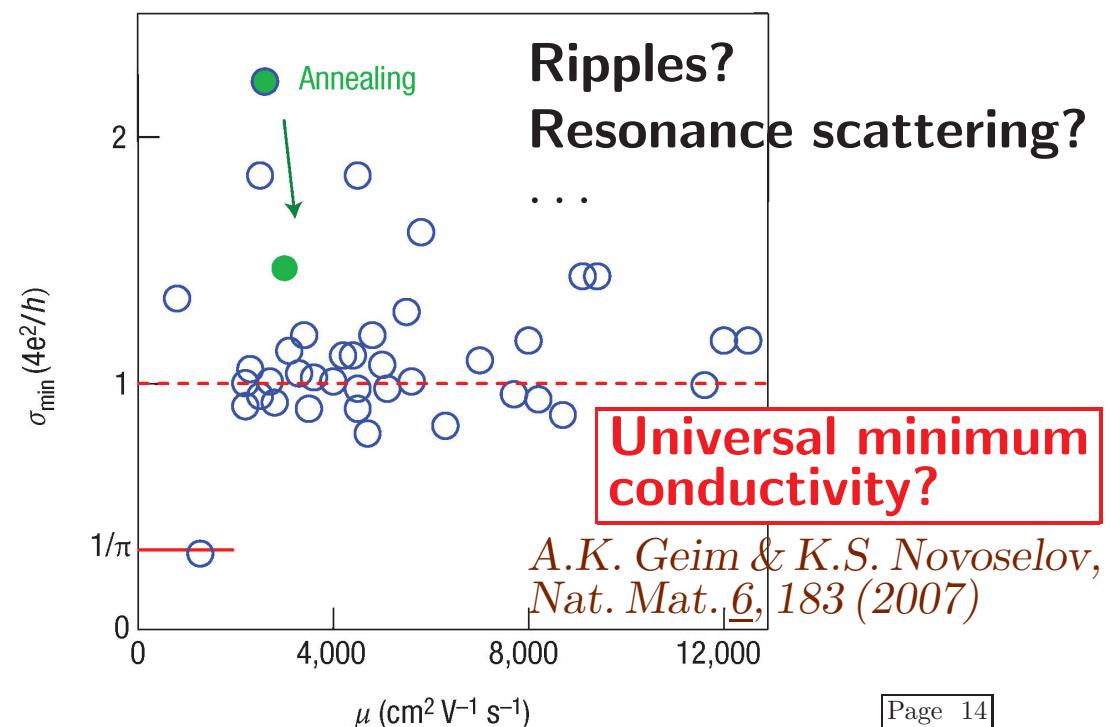
Scattering mechanisms

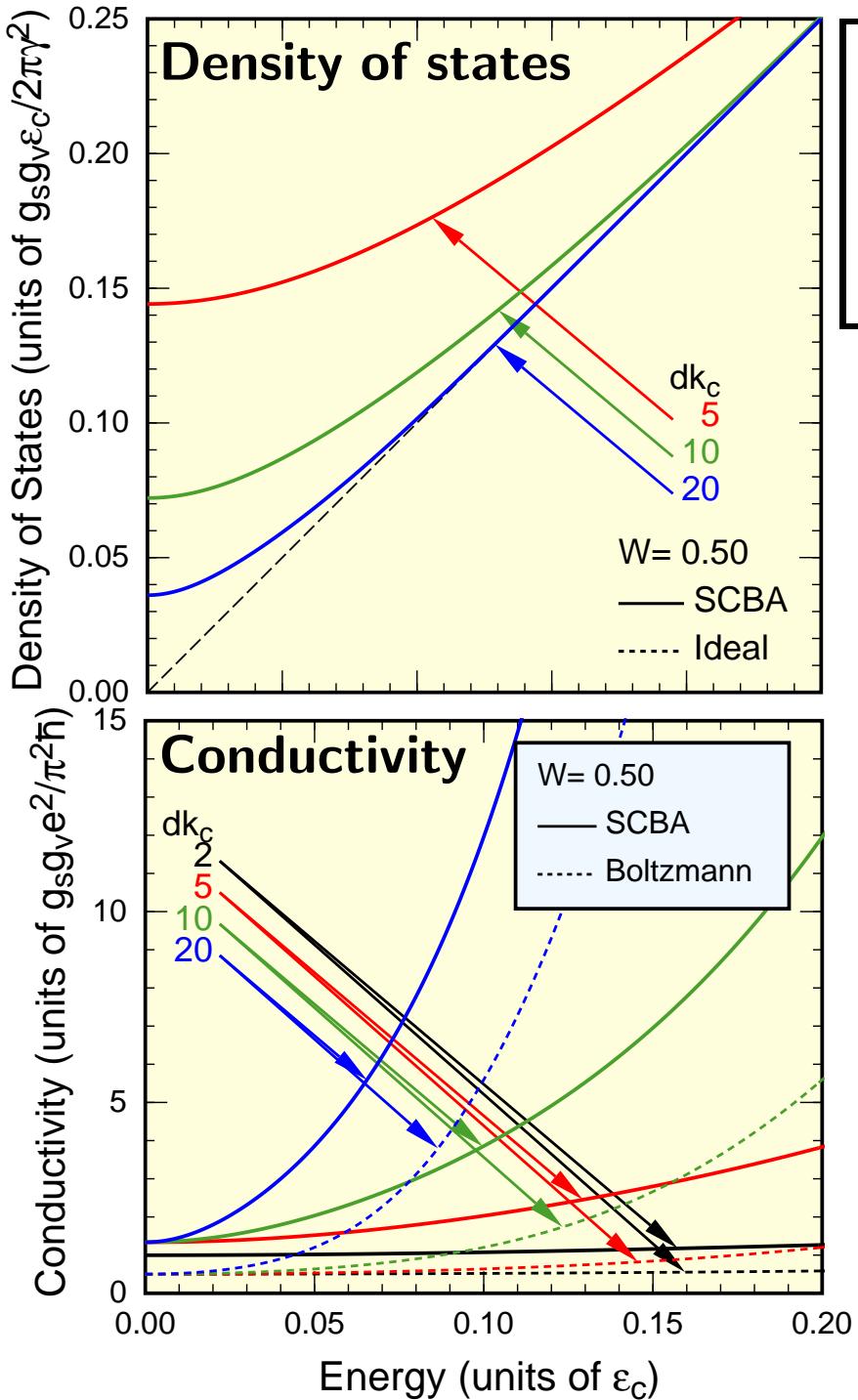
Boltzmann conductivity $\sigma(\epsilon_F) = \frac{e^2}{\pi^2 \hbar} \frac{1}{4W}$

Constant mobility $\Leftrightarrow W \propto n_s^{-1}$

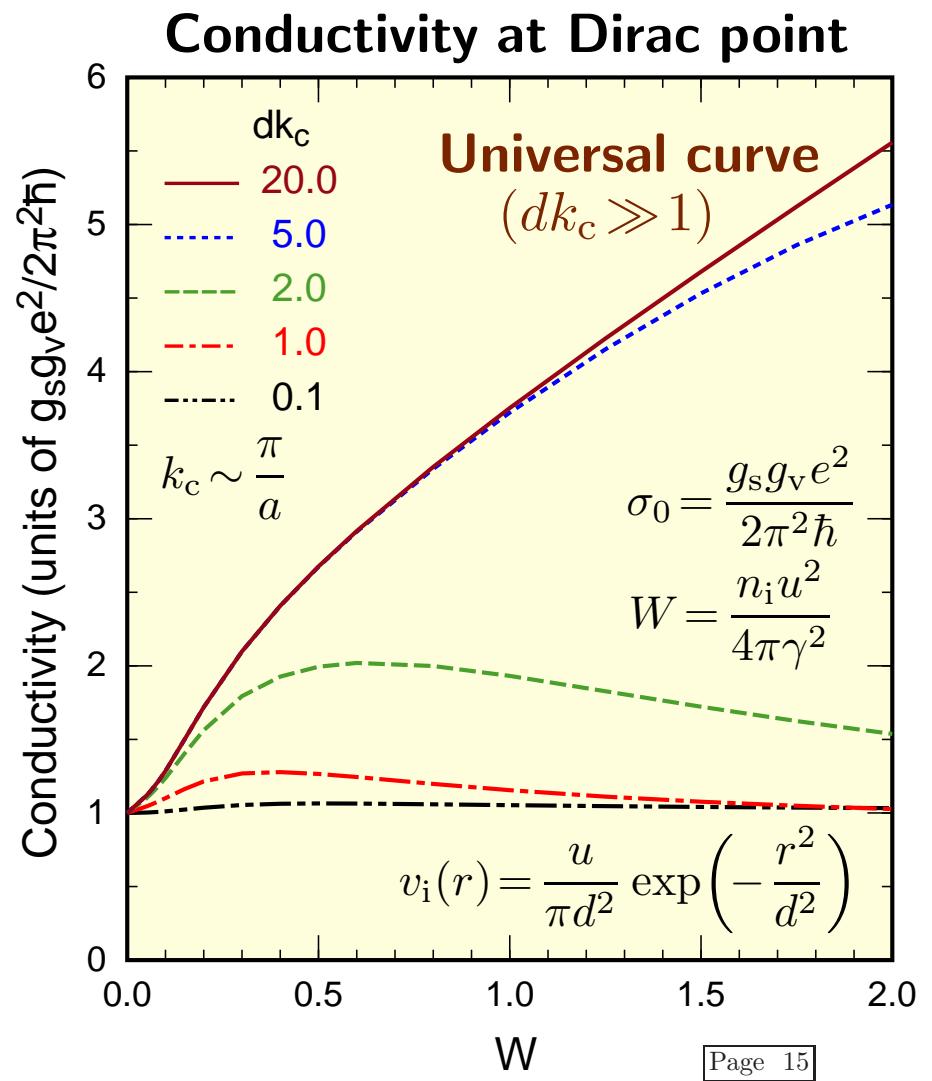
Charged impurity with screening

- T. Ando, *JPSJ* 75, 074716 (2006)
- K. Nomura & A.H. MacDonald, *PRL* 96, 256602 (2006)



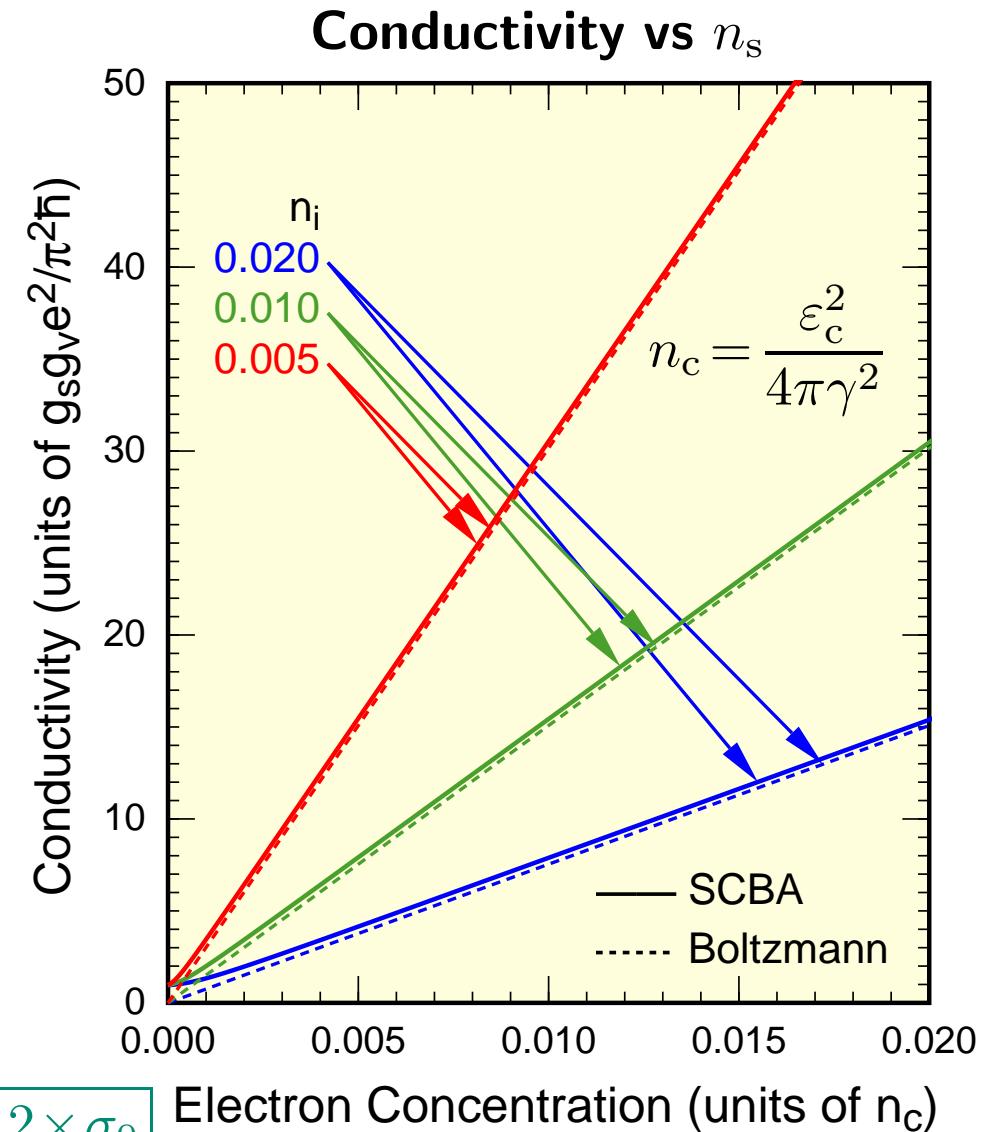
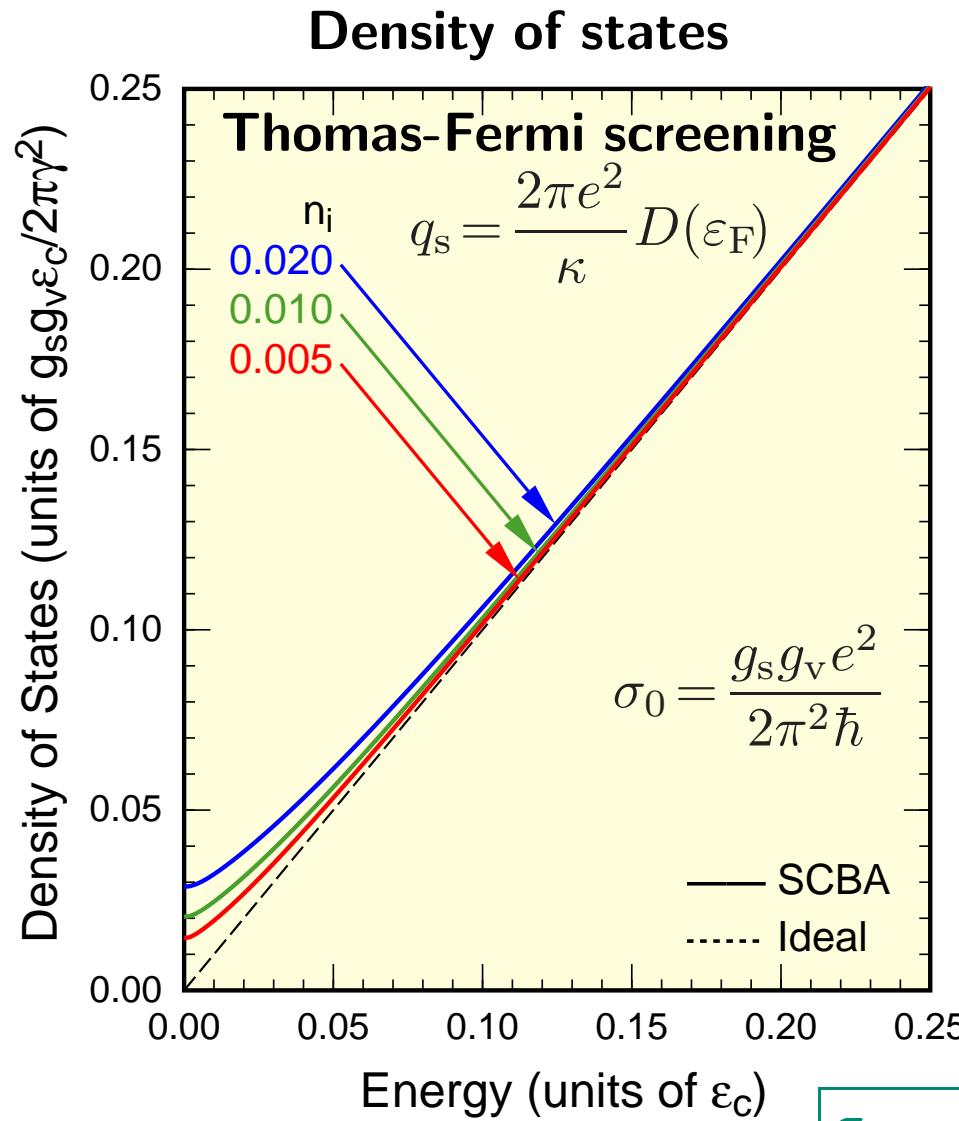


**Scatterers with Gaussian Potential
(Self-Consistent Born Approx.)**
[M. Noro, M. Koshino & T. Ando
JPSJ 79, 094713 (2010)]



Charged Impurities (Self-Consistent Born Approximation)

[M. Noro, M. Koshino & T. Ando, J. Phys. Soc. Jpn. 79, 094713 (2010)]

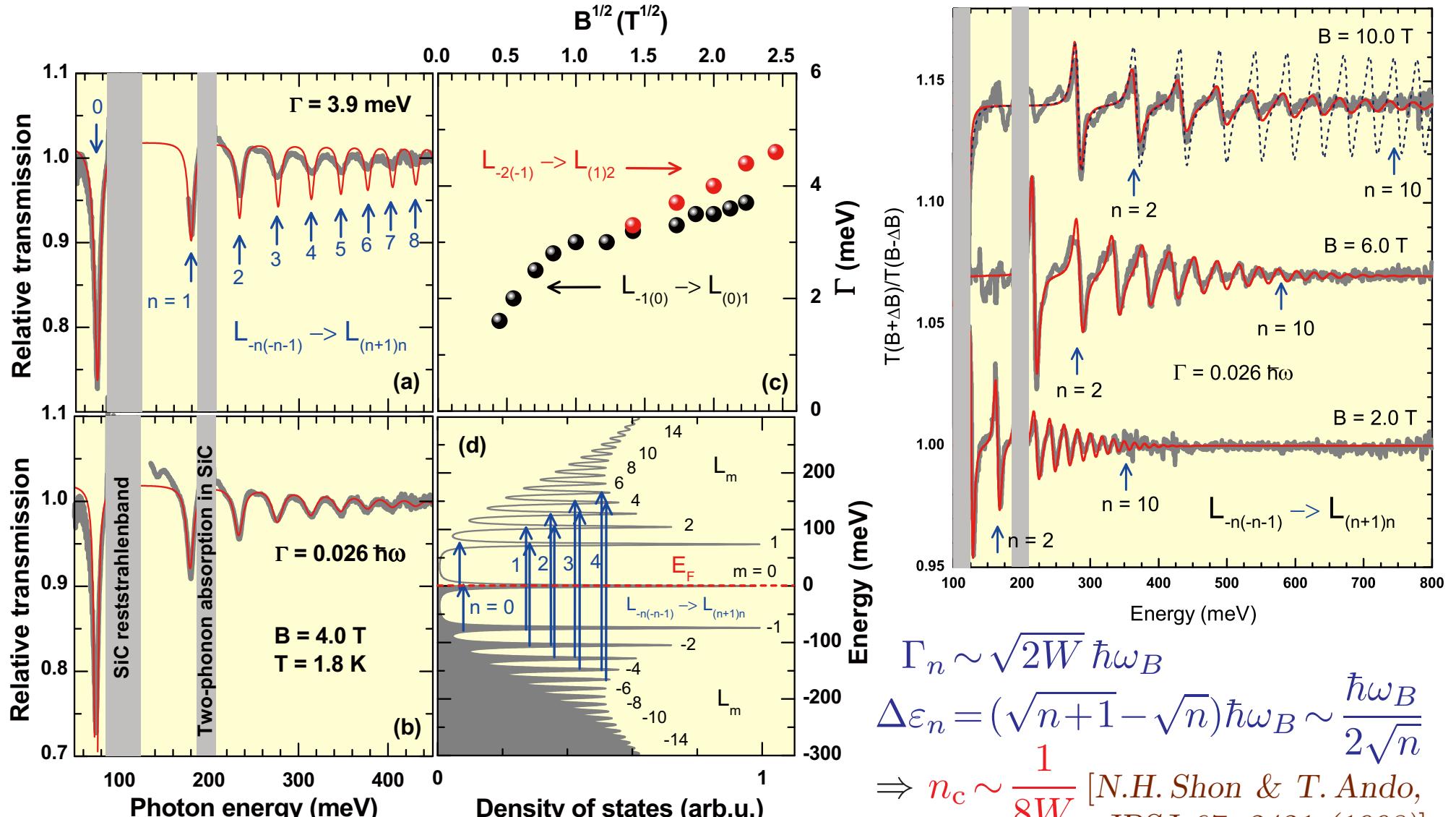


cf: X.-Z. Yan & C.S. Ting
Phys. Rev. B 80, 155423 (2009)

$$\sigma_{\min} \sim 2 \times \sigma_0$$

Interband Magnetoabsorption in Epitaxial Graphene

$\tau^{-1} \propto |\varepsilon|$ [M. Orlita et al., Phys. Rev. Lett. 107, 216603 (2011)]

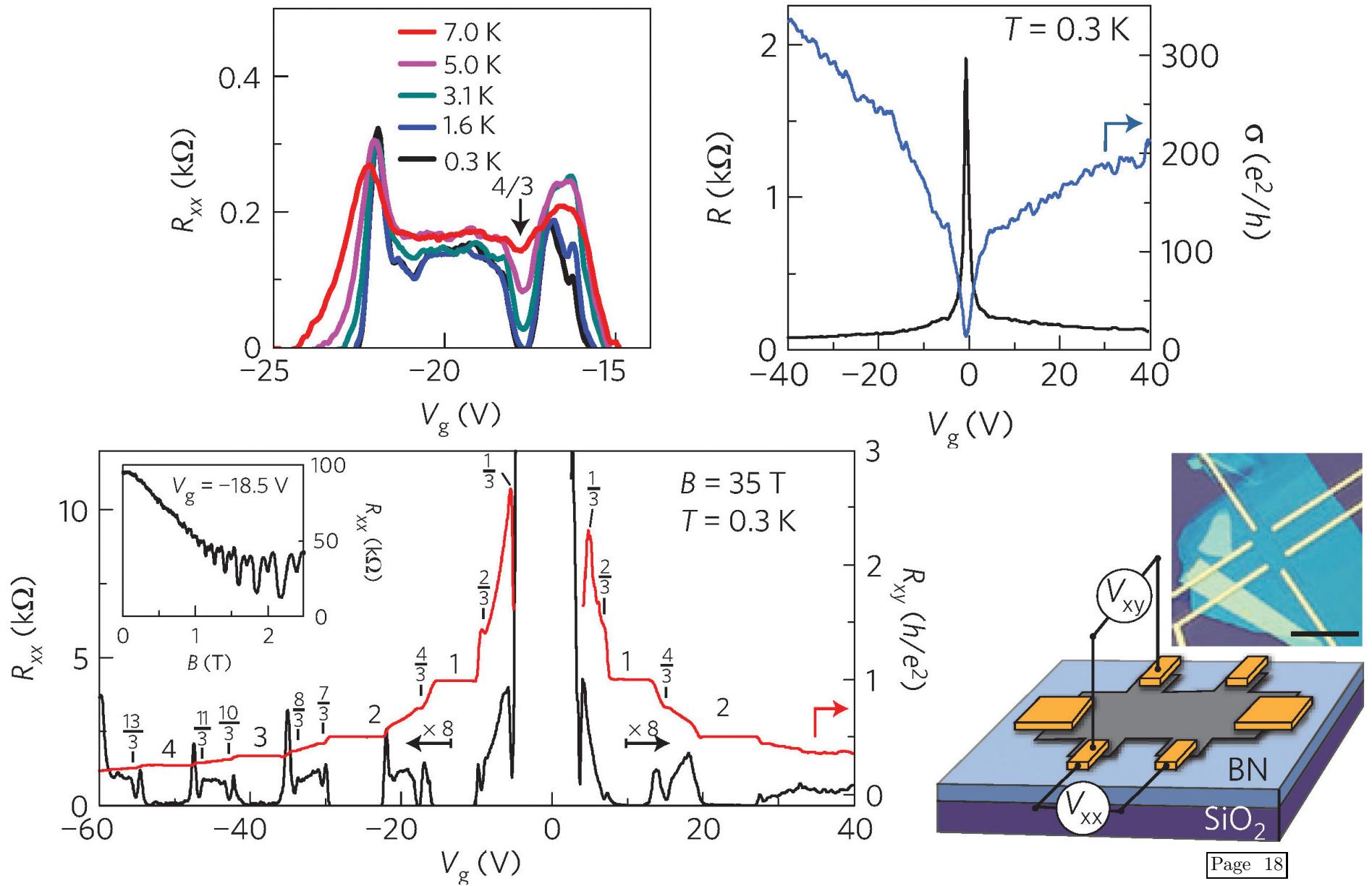


Suspended, BN substrate, CVD grown, ...

$$\begin{aligned}\Gamma_n &\sim \sqrt{2W} \hbar\omega_B \\ \Delta\varepsilon_n &= (\sqrt{n+1} - \sqrt{n}) \hbar\omega_B \sim \frac{\hbar\omega_B}{2\sqrt{n}} \\ \Rightarrow n_c &\sim \frac{1}{8W} [N.H. Shon \& T. Ando, JPSJ 67, 2421 (1998)]\end{aligned}$$

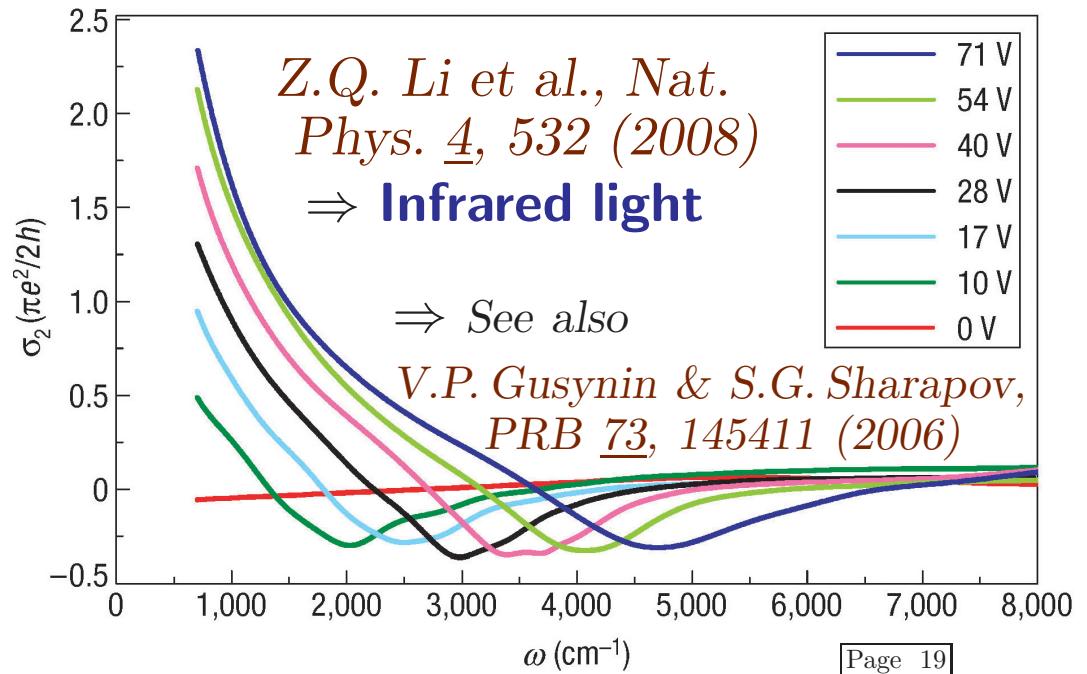
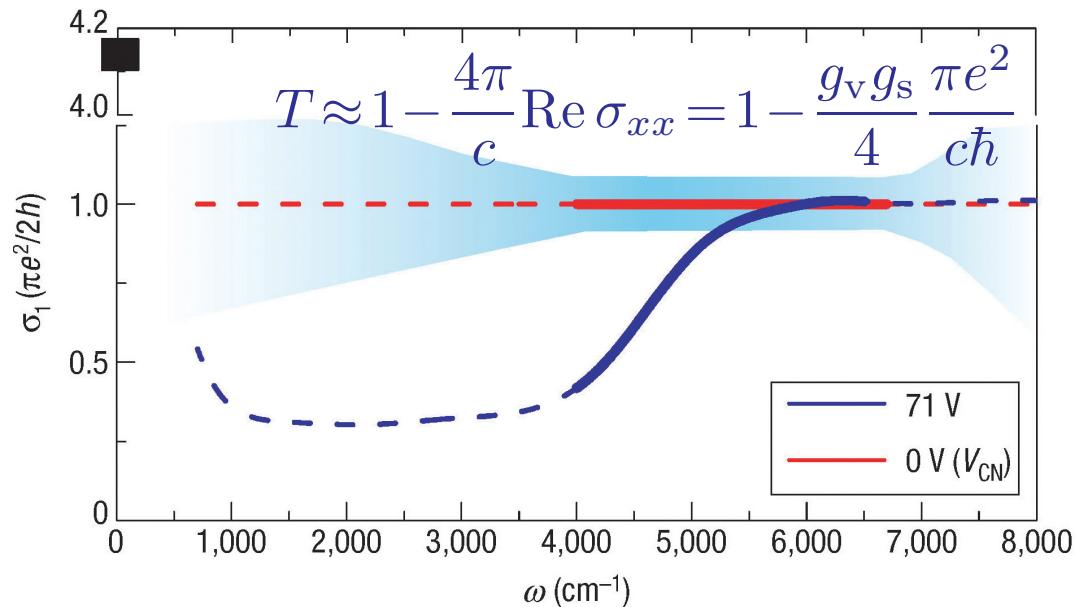
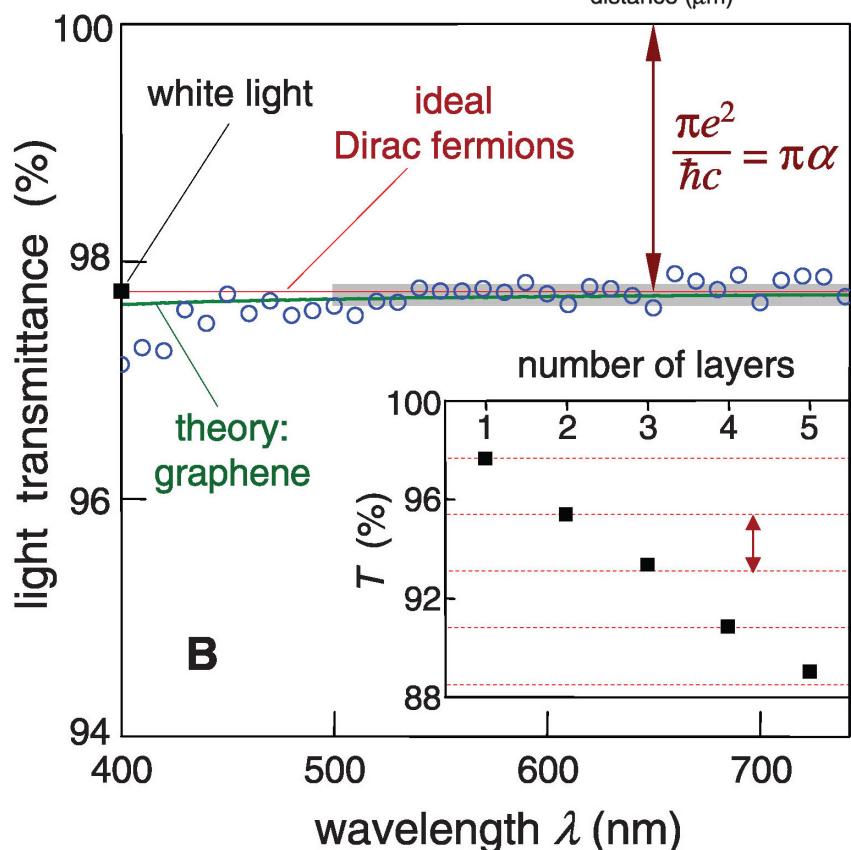
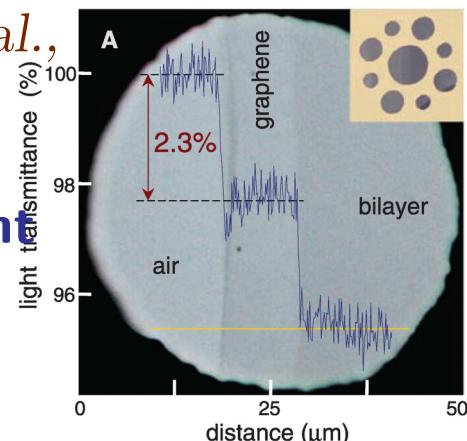
Fractional Quantum Hall Effect (BN Substrate)

[C.R. Dean et al., Nat. Phys. 7, 693 (2011)]



Dynamical Conductivity: Experiments

R.R. Nair et al.,
Science 320,
1308 (2008)
⇒ Visible light



Bilayer Graphene: AB Stacking (Bernal Stacking)

Quantum Hall effect in bilayer graphene

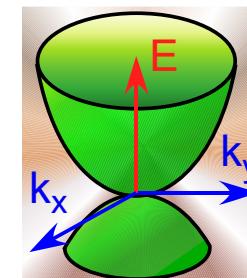
K.S. Novoselov et al., *Nature* 438, 197 (2005)

K.S. Novoselov et al., *Nat. Phys.* 2, 177 (2006)

ARPES [T. Ohta et al., *PRL* 98, 206802 (2007)]

Effective Hamiltonian in bilayer graphene

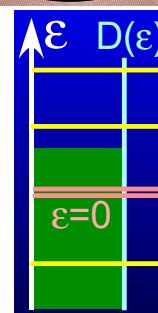
$$\mathcal{H} = \begin{pmatrix} A_1 & B_1 & A_2 & B_2 \\ 0 & \gamma \hat{k}_- & 0 & 0 \\ \gamma \hat{k}_+ & 0 & \Delta & 0 \\ 0 & \Delta & 0 & \gamma \hat{k}_- \\ 0 & 0 & \gamma \hat{k}_+ & 0 \end{pmatrix} \quad \hat{k}_{\pm} = \hat{k}_x \pm i \hat{k}_y \quad \Delta = \gamma_1 \approx 0.4 \text{ eV}$$



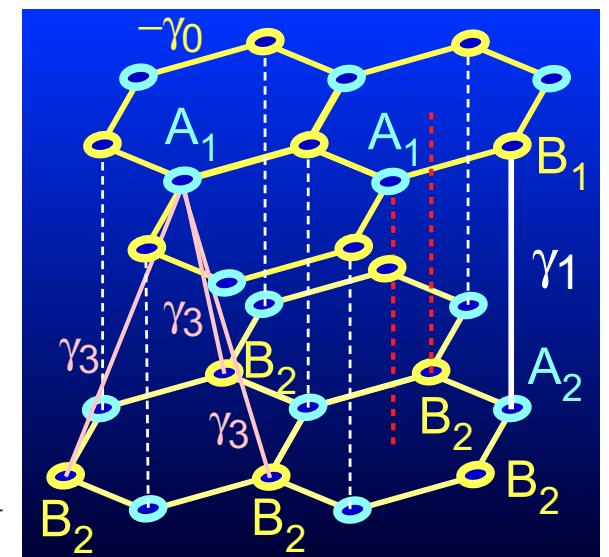
$$\mathcal{H} \approx \frac{\hbar^2}{2m^*} \begin{pmatrix} 0 & \hat{k}_-^2 \\ \hat{k}_+^2 & 0 \end{pmatrix} \quad m^* = \frac{\hbar^2 \Delta}{2\gamma^2}$$

$$\varepsilon_n = \pm \hbar \omega_c \sqrt{n(n+1)} \quad (n=0, 1, \dots)$$

\Rightarrow Two Landau levels at $\varepsilon=0$



Susceptibility $\Rightarrow \chi(\varepsilon) = -\frac{g_v g_s}{4\pi} \frac{e^2 \gamma}{c^2 \hbar^2} \ln \left| \frac{\Delta}{\varepsilon} \right|$ [S.A. Safran, *PRB* 30, 421 (1984)]



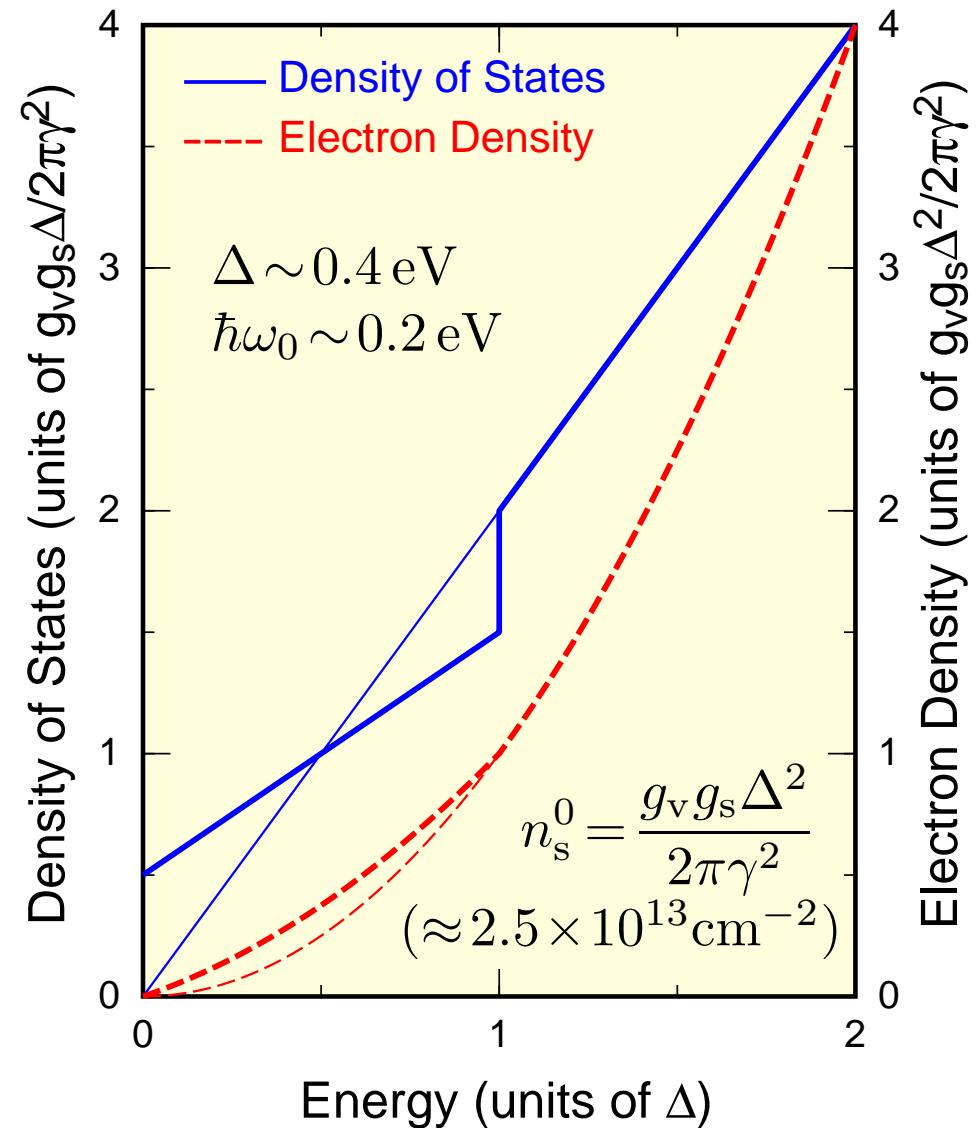
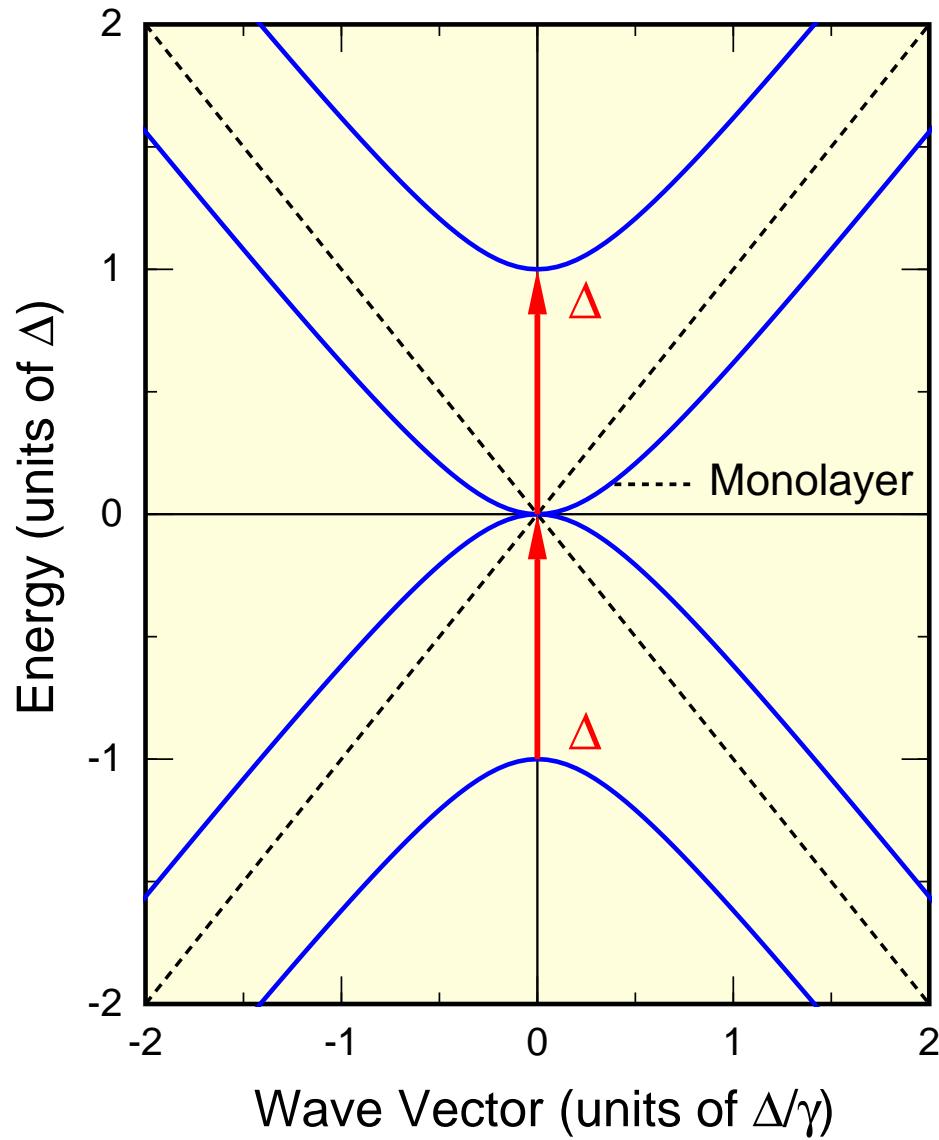
- E. McCann and V.I. Falko, *PRL* 96, 086805 (2006)
- M. Koshino and T. Ando, *PRB* 73, 245403 (2006)

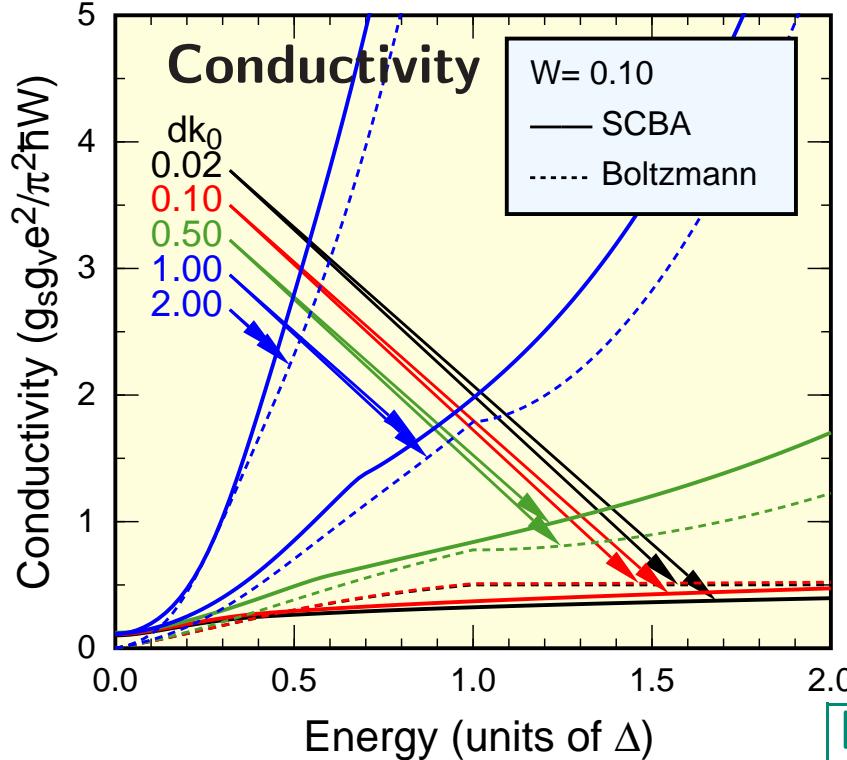
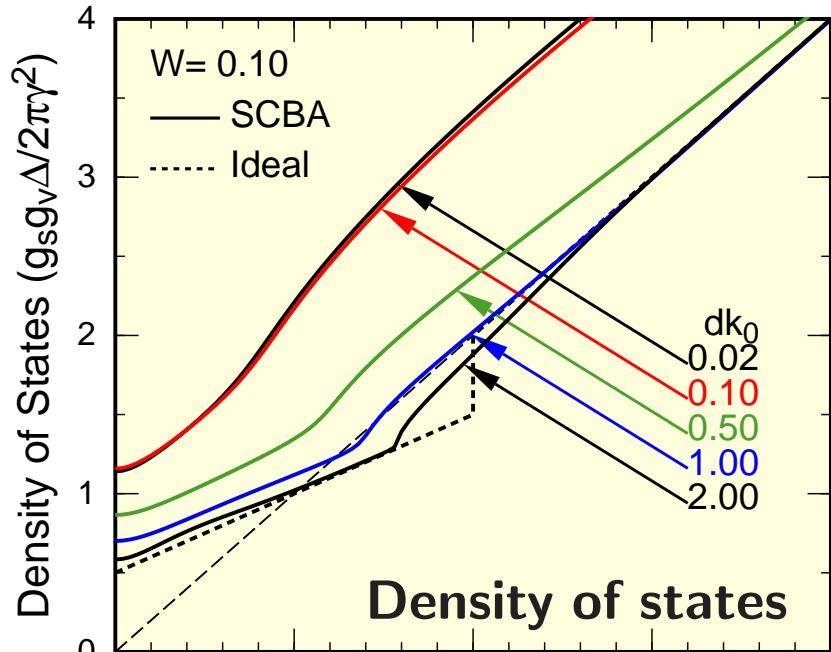
Tight-binding models

- S. Latil and L. Henrard, *PRL* 97, 036803 (2006)
- F. Guinea et al., *PRB* 73, 245426 (2006), ...

Energy Dispersion and Density of States of Bilayer Graphene

T. Ando, J. Phys. Soc. Jpn. 76, 104711 (2007)



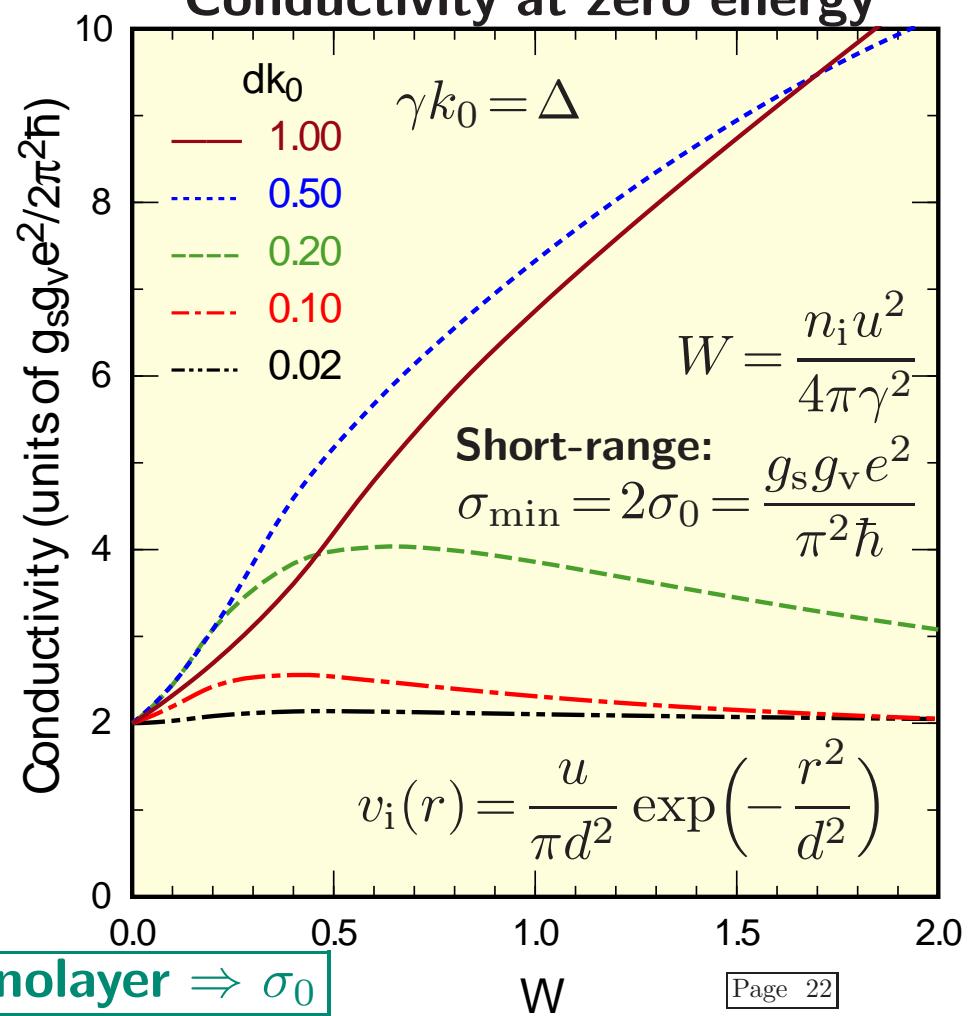


Scatterers with Gaussian Potential (Self-Consistent Born Approx.)

[T. Ando, JPSJ 80, 014707 (2011)]

Short-range: M. Koshino & T. Ando,
PRB 73, 245403 (2006)

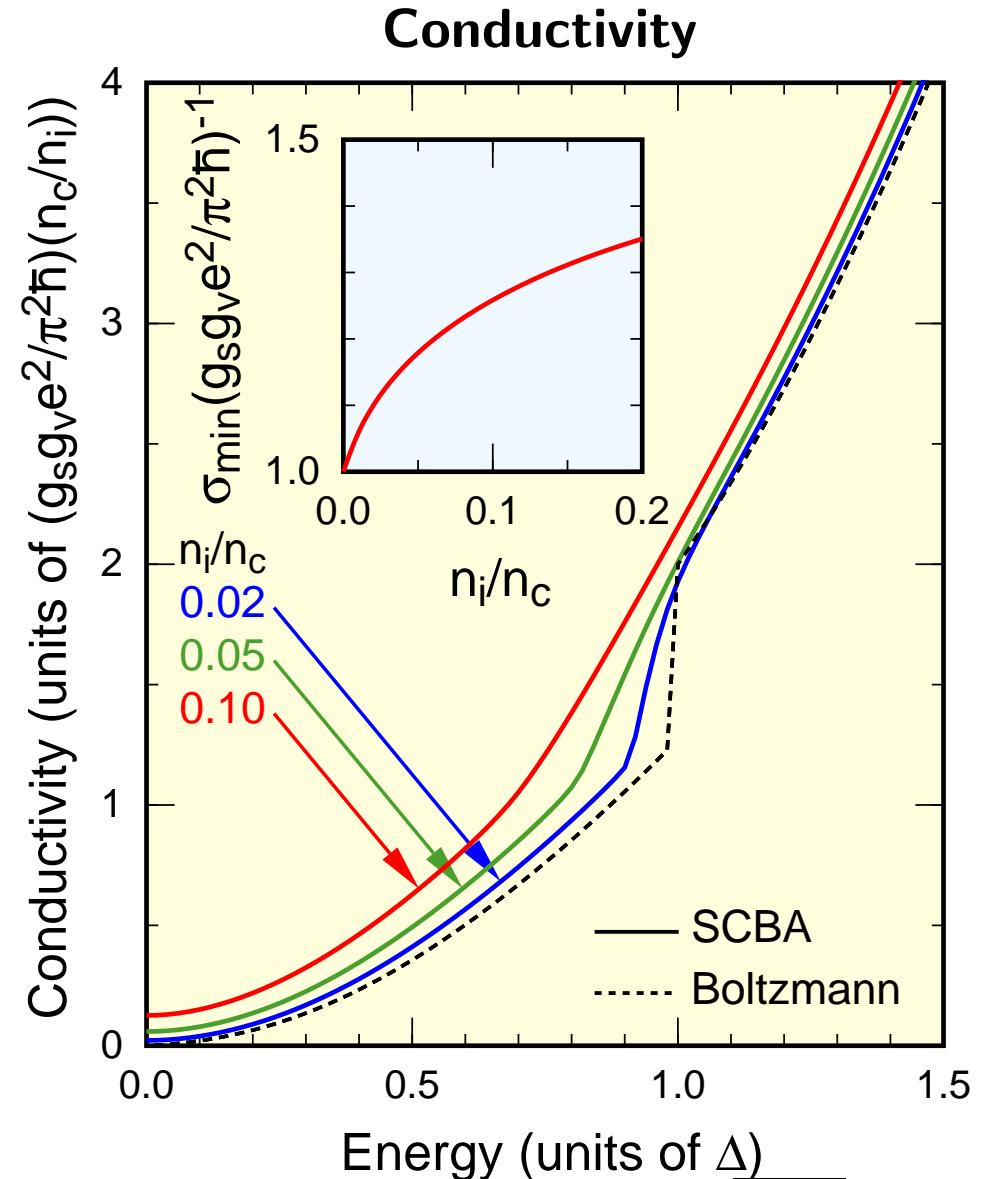
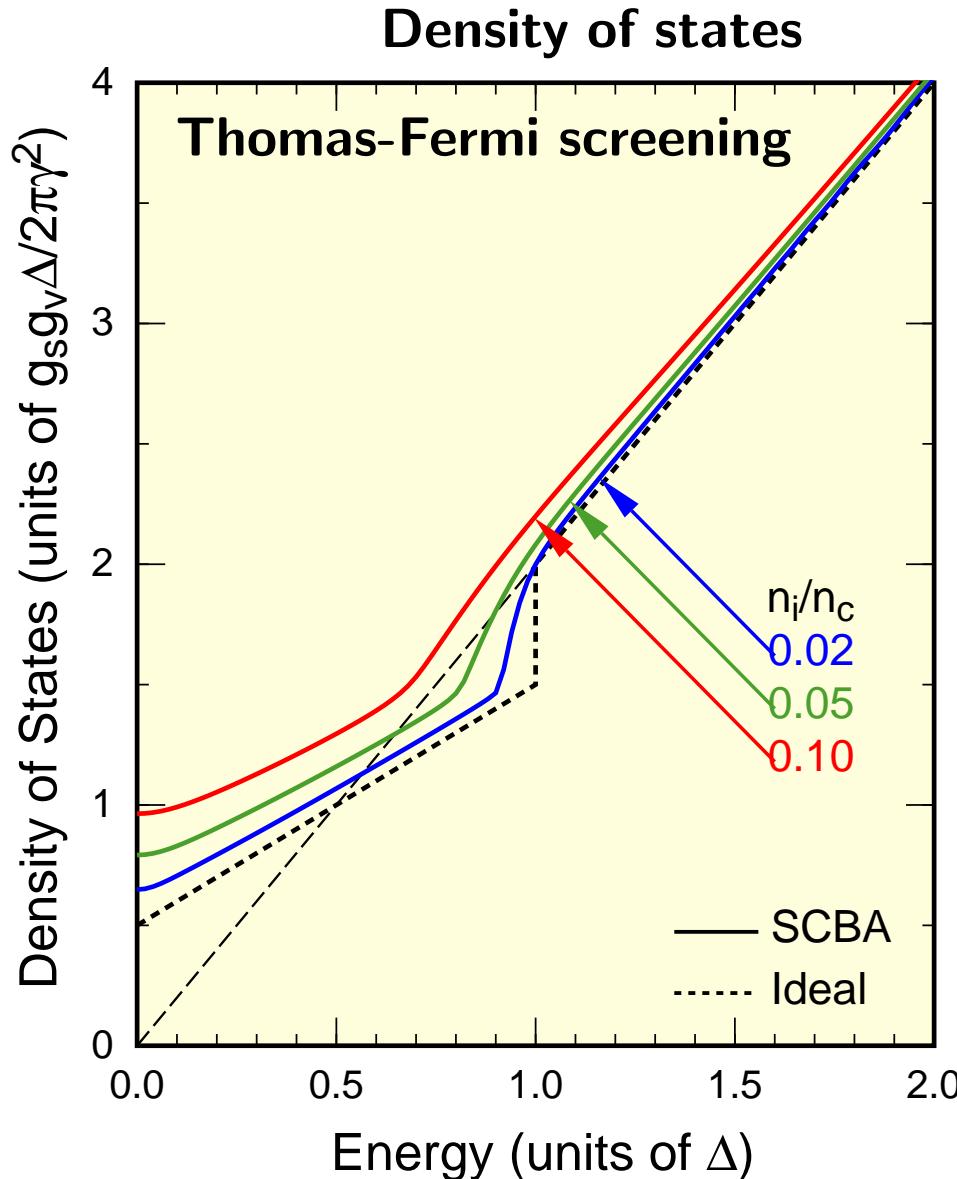
Conductivity at zero energy



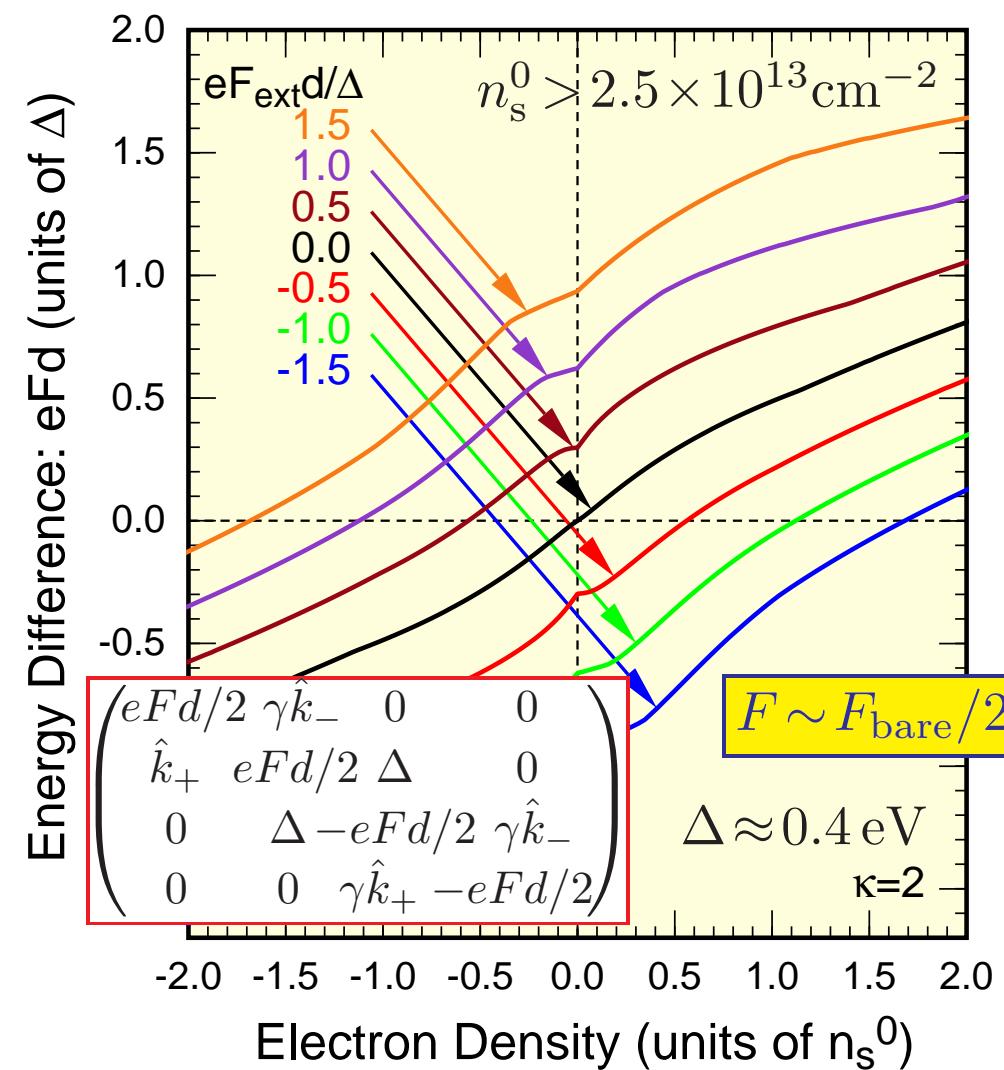
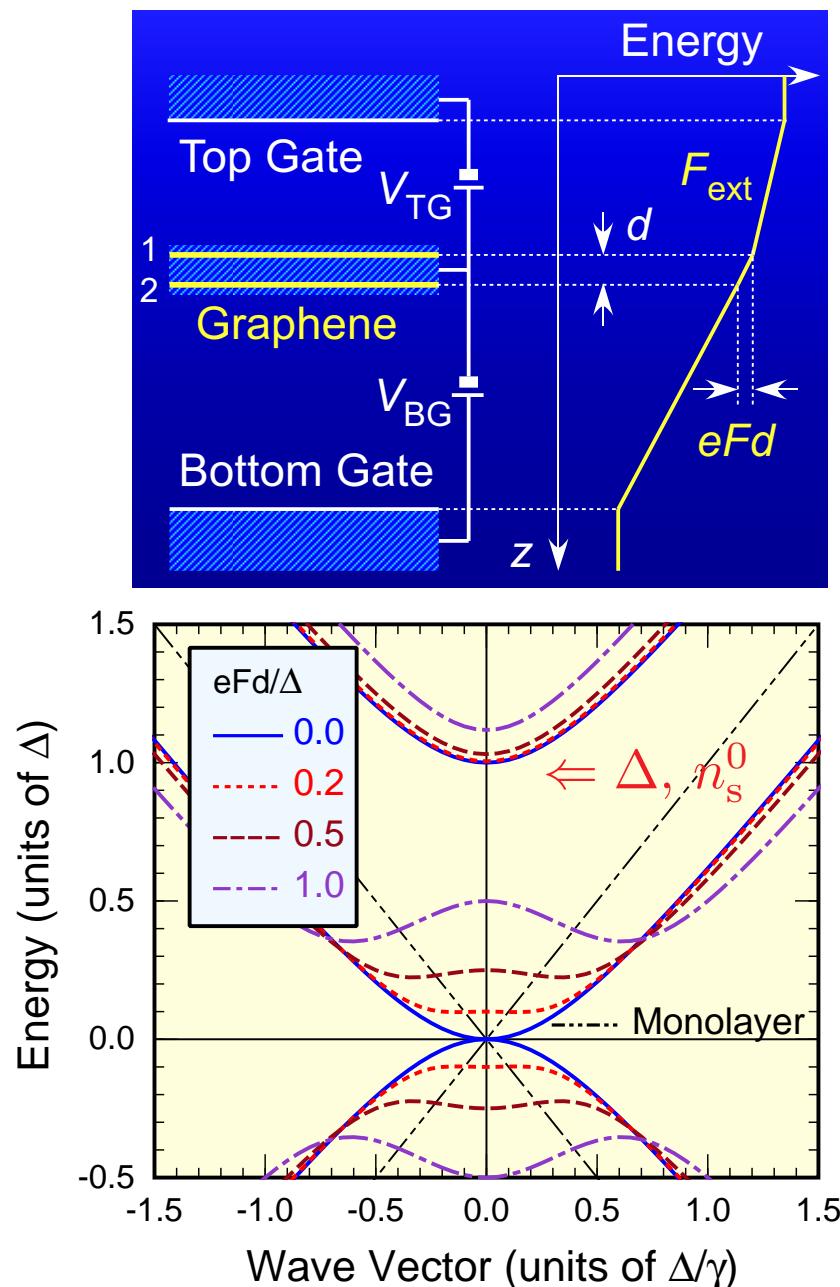
Monolayer $\Rightarrow \sigma_0$

Charged Impurities (Self-Consistent Born Approximation)

[T. Ando, J. Phys. Soc. Jpn. 80, 014707 (2011)]



Field Effect on Energy Spectrum in Bilayer Graphene



- E. McCann, PRB 74, 161403 (2006)
H. Min et al., PRB 75, 155115 (2007)
T. Ando & M. Koshino, JPSJ 78, 034709 (2009)

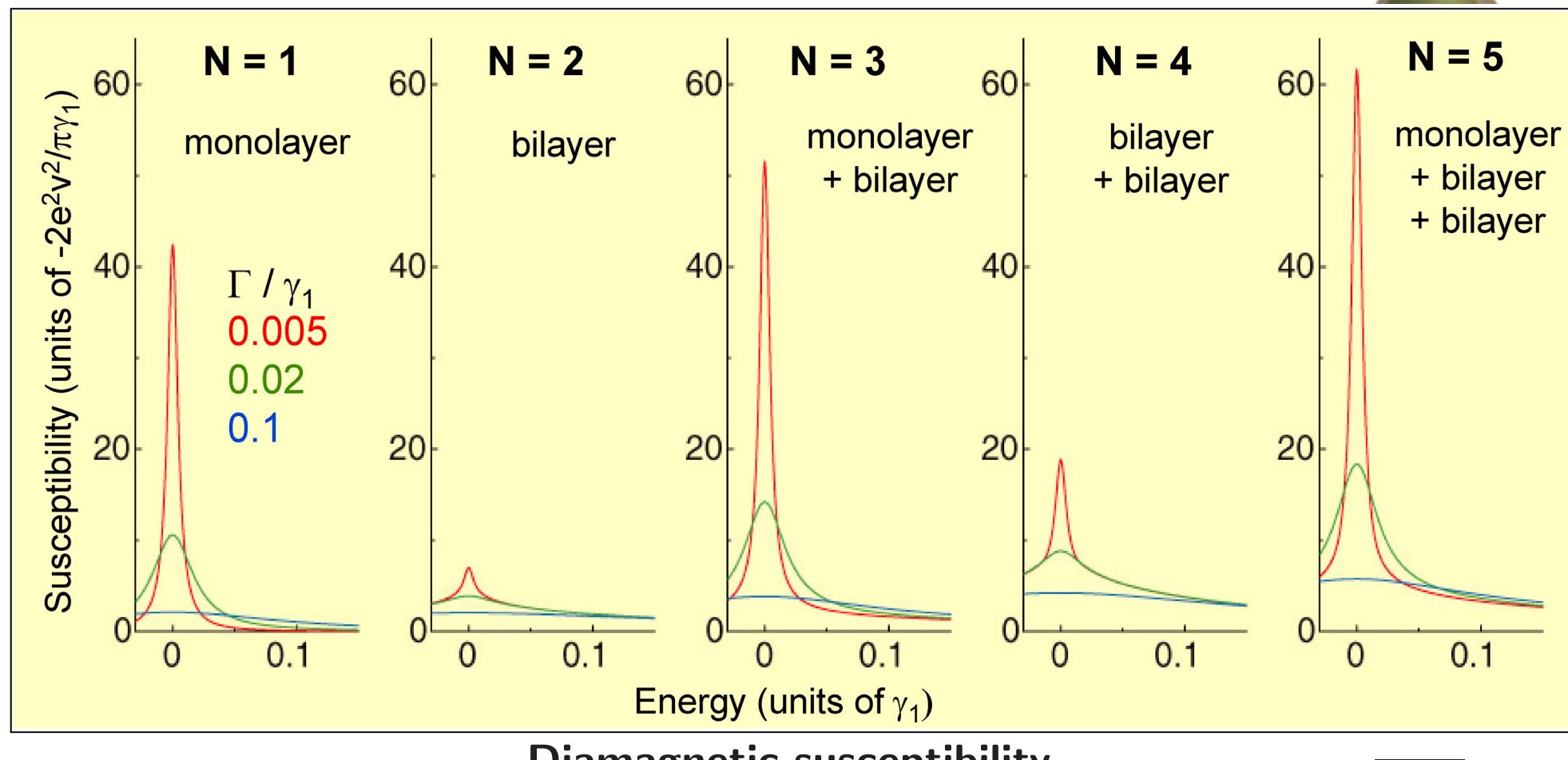
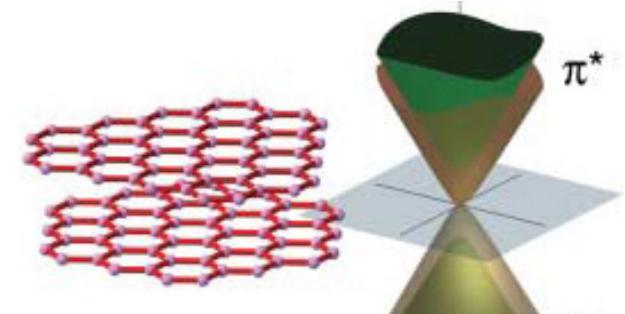
Multi-Layer Graphene [M. Koshino & T. Ando, PRB 76, 085425 (2007)]

Exact decomposition of effective Hamiltonian

$2M+1$ Layers = $1 \times$ Monolayer + $M \times$ Bilayers

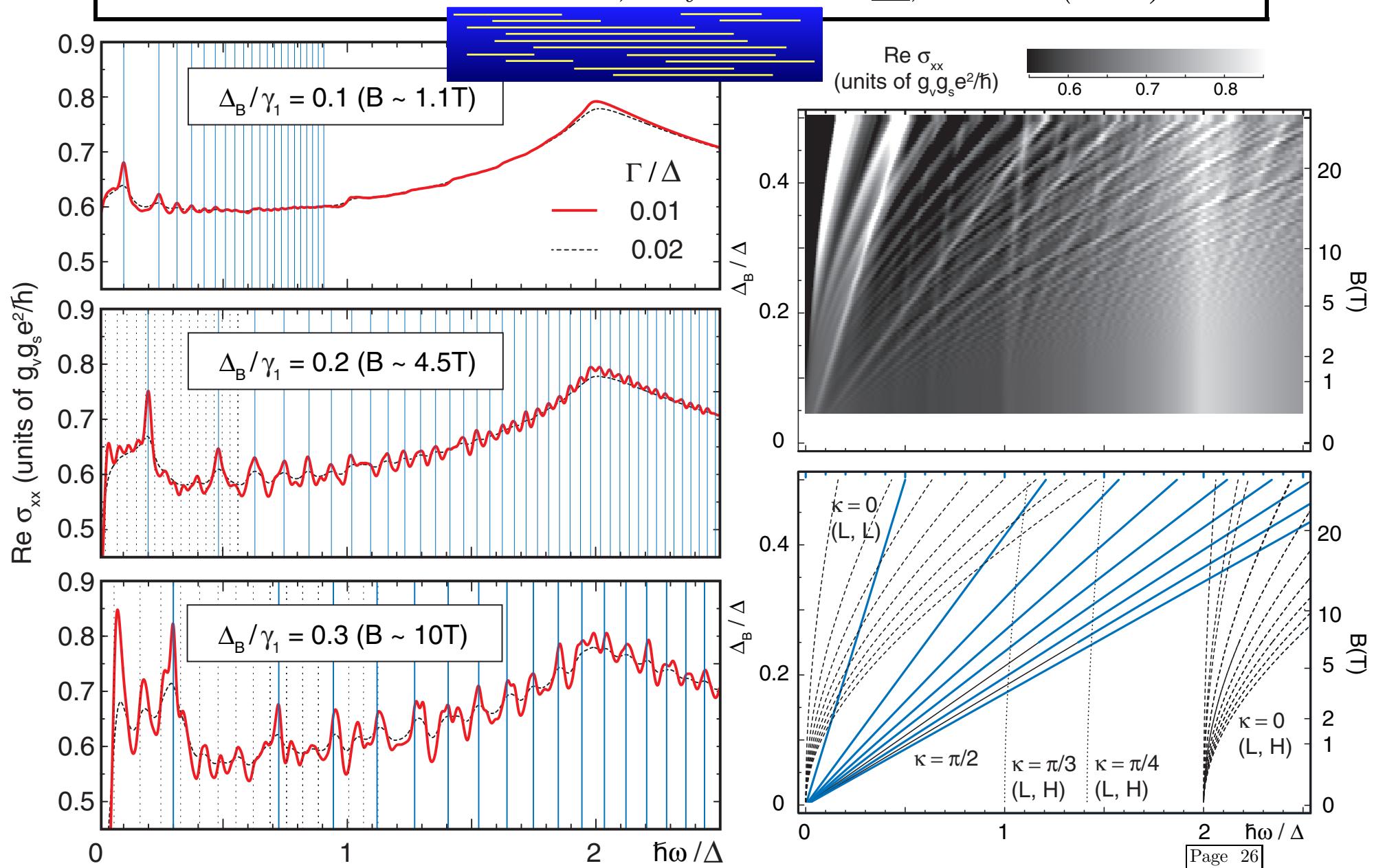
$2M$ Layers = $0 \times$ Monolayer + $M \times$ Bilayers

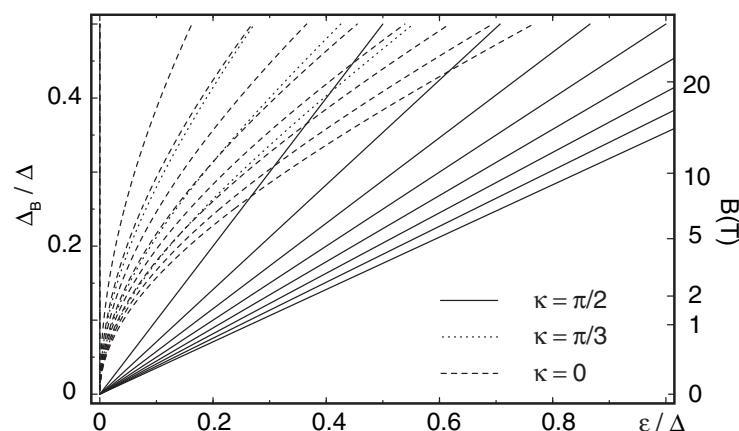
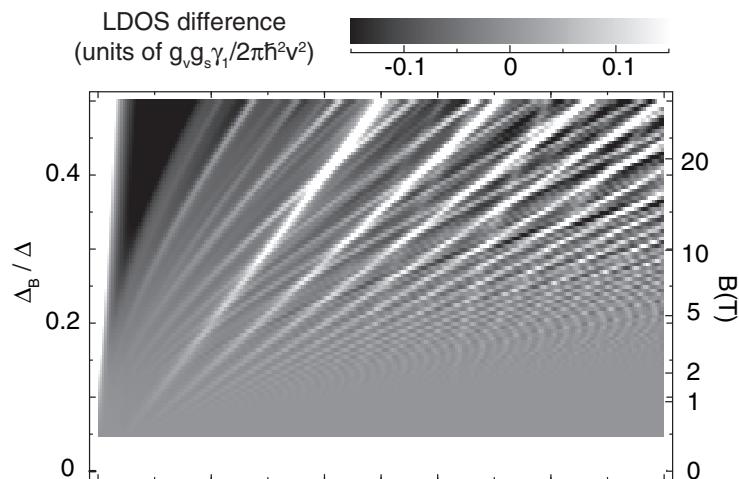
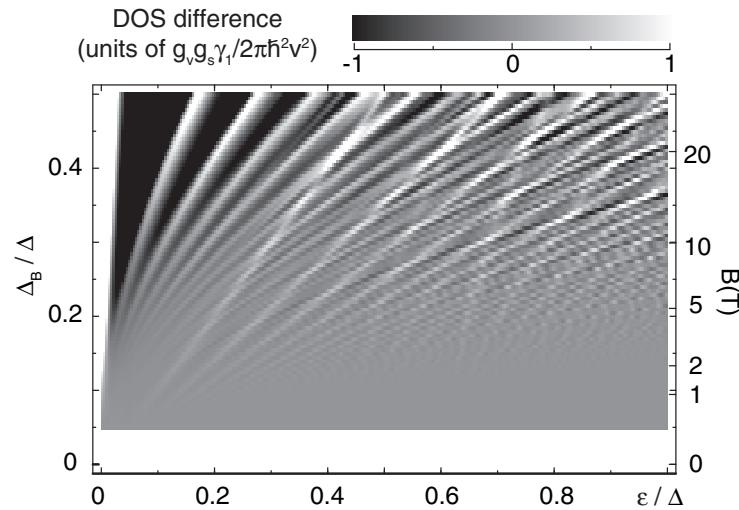
Three parameters: γ_0 , γ_1 , γ_3 (trigonal warping)



Dynamical Conductivity of Multi-Layer Graphene (Average 1–20)

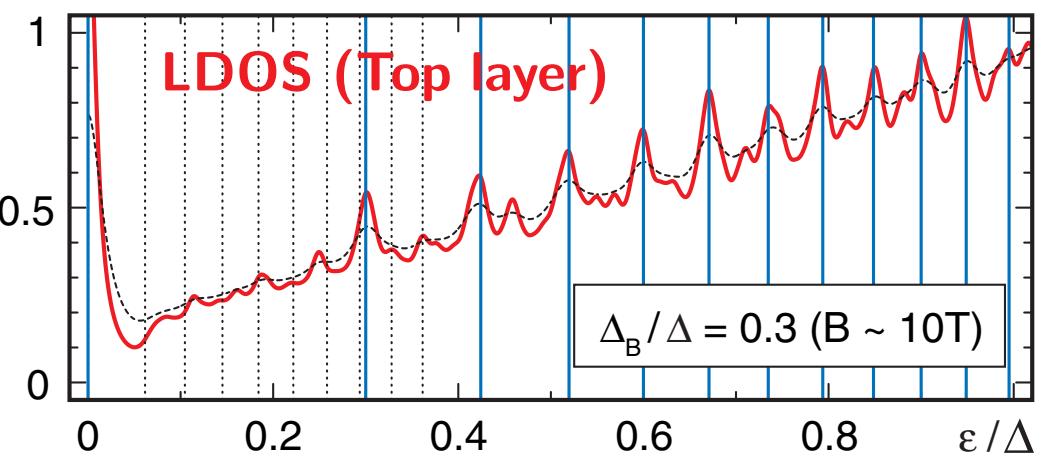
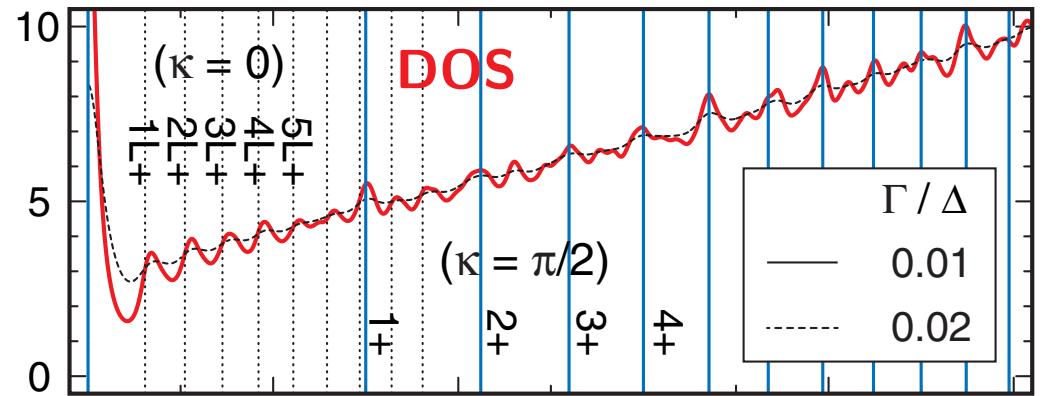
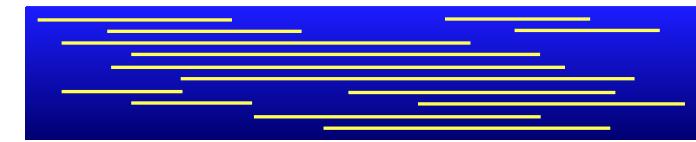
M. Koshino and T. Ando, Phys. Rev. B 77, 115313 (2008)





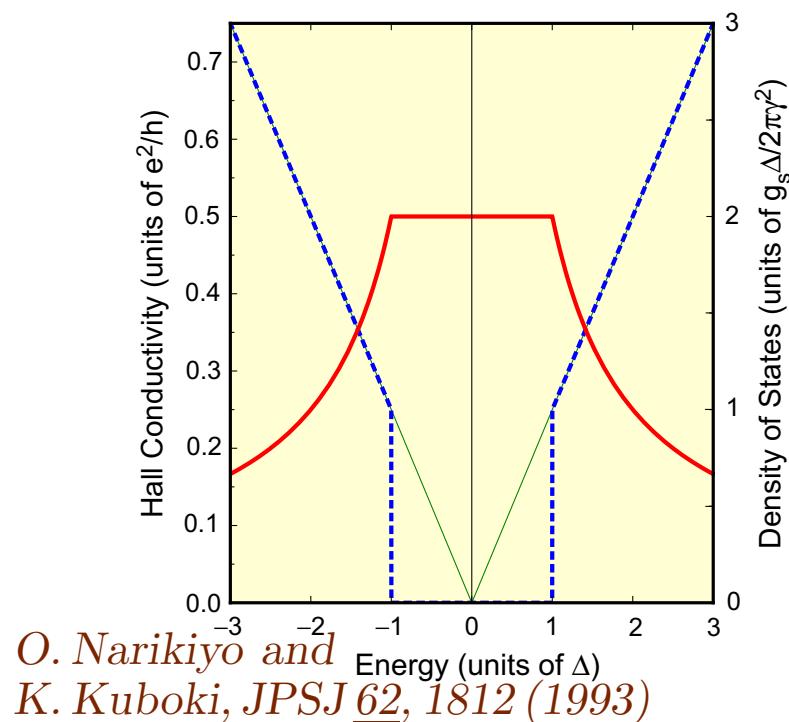
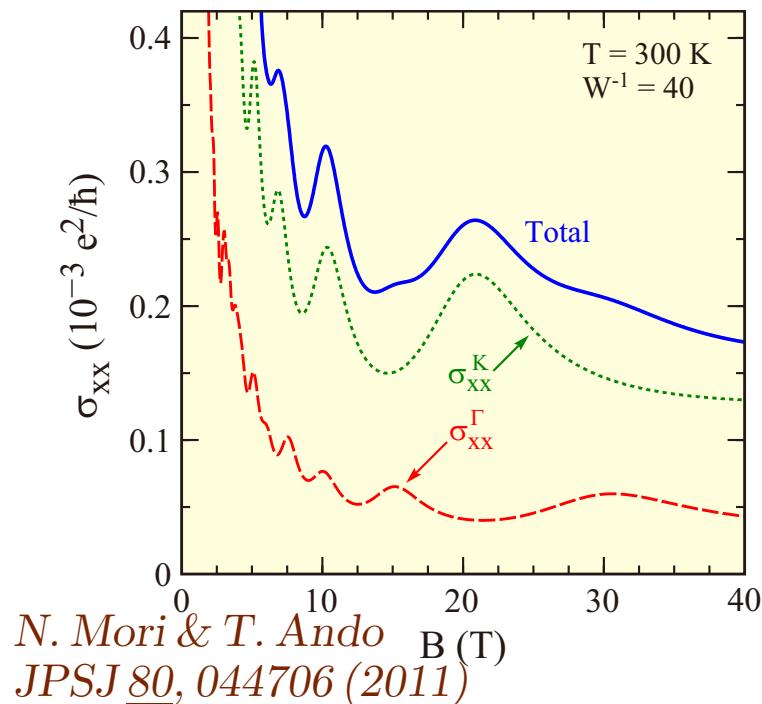
Local Density of States of Multi-Layer Graphene (Average 1–20)

M. Koshino and T. Ando,
Phys. Rev. B 77, 115313 (2008)

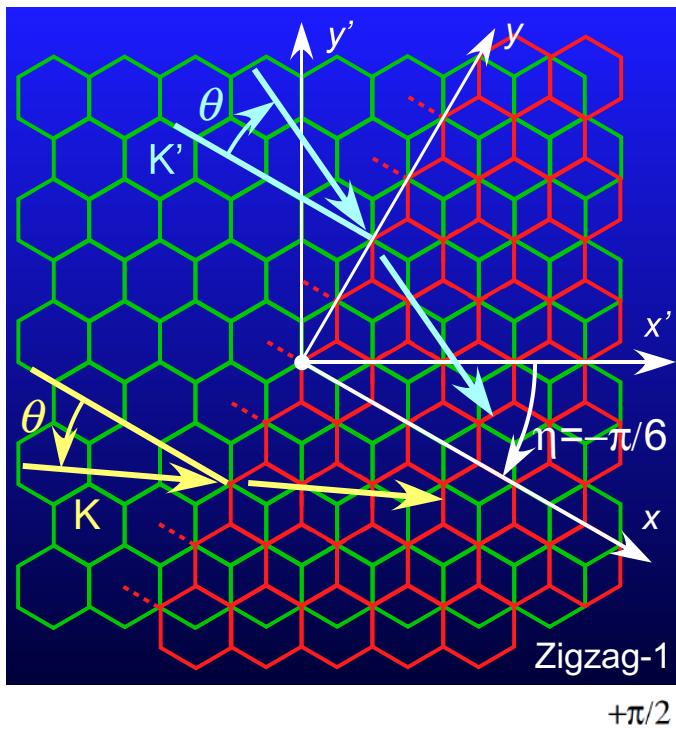
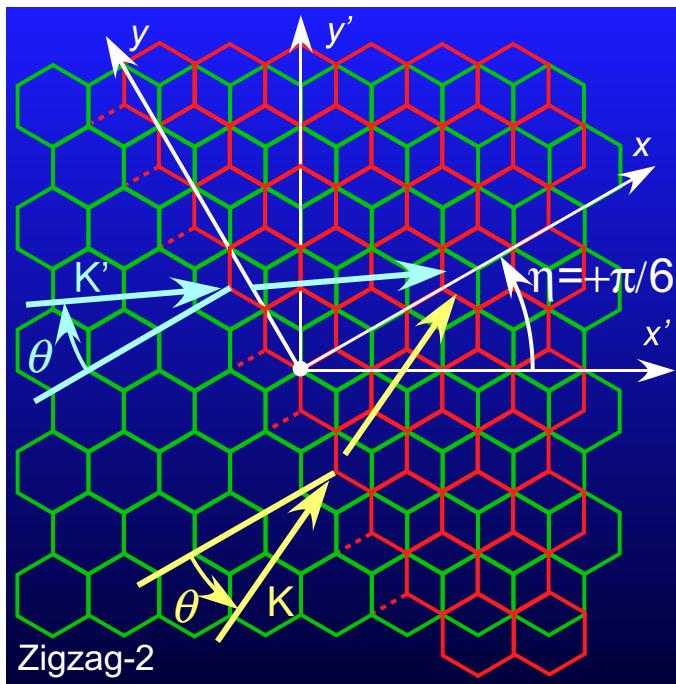


Further Developments and Future Outlook

1. Time reversal symmetry and crossover
2. Electron-phonon interaction, Gauge field, instabilities, ···
 - Optical phonon anomaly
 - Pseudo Landau levels
 - ↑ Magnetophonon resonances
3. Electron-electron interaction
4. Band gap and valley polarization
 - Substrate effects
 - Orbital magnetism
 - ↑ Chiral anomaly (Hall effect without B , ...)
 - Chiral edge states
 - Exotic phenomena
5. Graphene ribbons
 - Chiral edge states

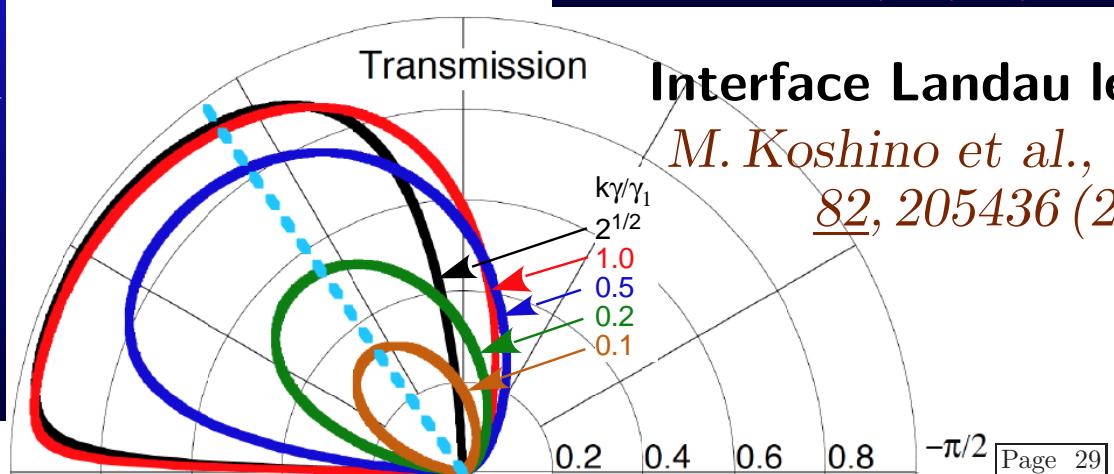
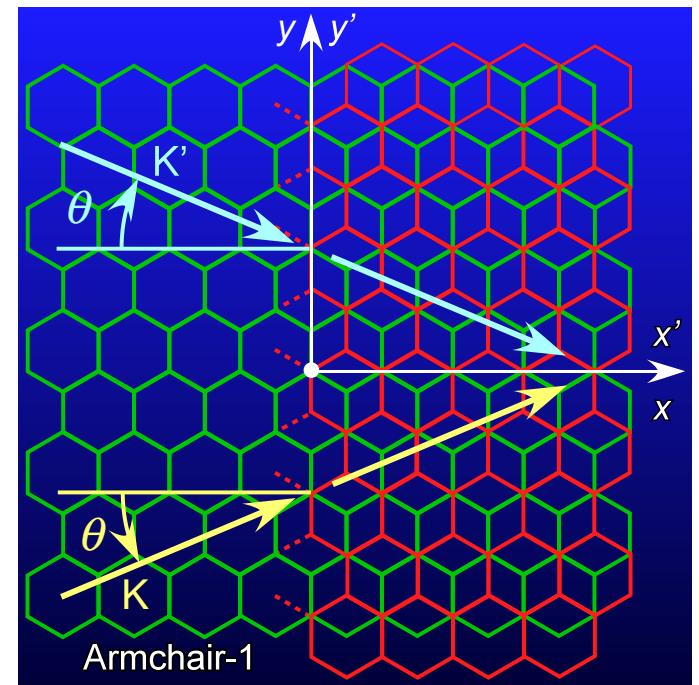


Transmission between Mono- and Bi-Layer Graphene [T. Nakanishi, M. Koshino, and T. Ando, PRB 82, 125428 (2010)]



Valley polarization

$$T_K(\theta) \gg T_{K'}(\theta) \quad (\theta > 0)$$



Summary: Electronic and Transport Properties of Graphene

Tsuneya ANDO

1. Introduction

- Weyl's equation for neutrino
- Berry's phase and topological anomaly

2. Singular diamagnetic susceptibility

- Band-gap effect
- Spatially varying magnetic field

3. Transport properties graphene

- Singularities at Dirac point
- Long-range scatterers

4. Multi-layer graphene

- Bilayer graphene
- Hamiltonian decomposition

5. Future outlook

- Gauge fields
- Chiral edge states

6. Summary

Nara, Jun 4 (Tue) 2013



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16th International Workshop on Computational
 Electronics, Nara Prefectural New Public Hall
 Jun 4 (Tue) – 7 (Fri) 2013 [13:30–14:30 (50+10)]